

# Astronomie et astrophysique pour physiciens CUSO 2015

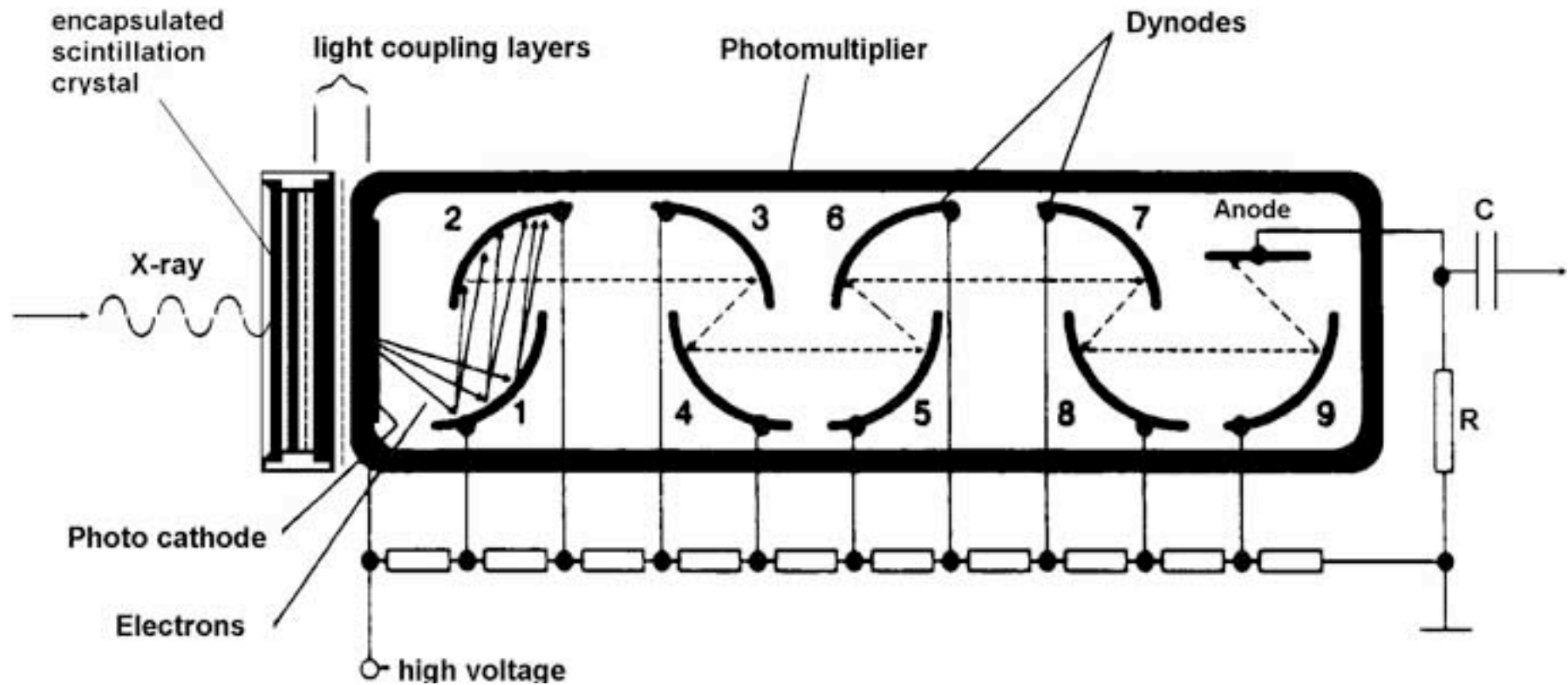
Instruments and observational techniques  
– Détecteurs

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Observatoire de l'Université Genève

F. Courbin and P. Jablonka, EPFL

# Photomultipliers



Gain of  $10^7$ - $10^9$

From Bruker-AXS

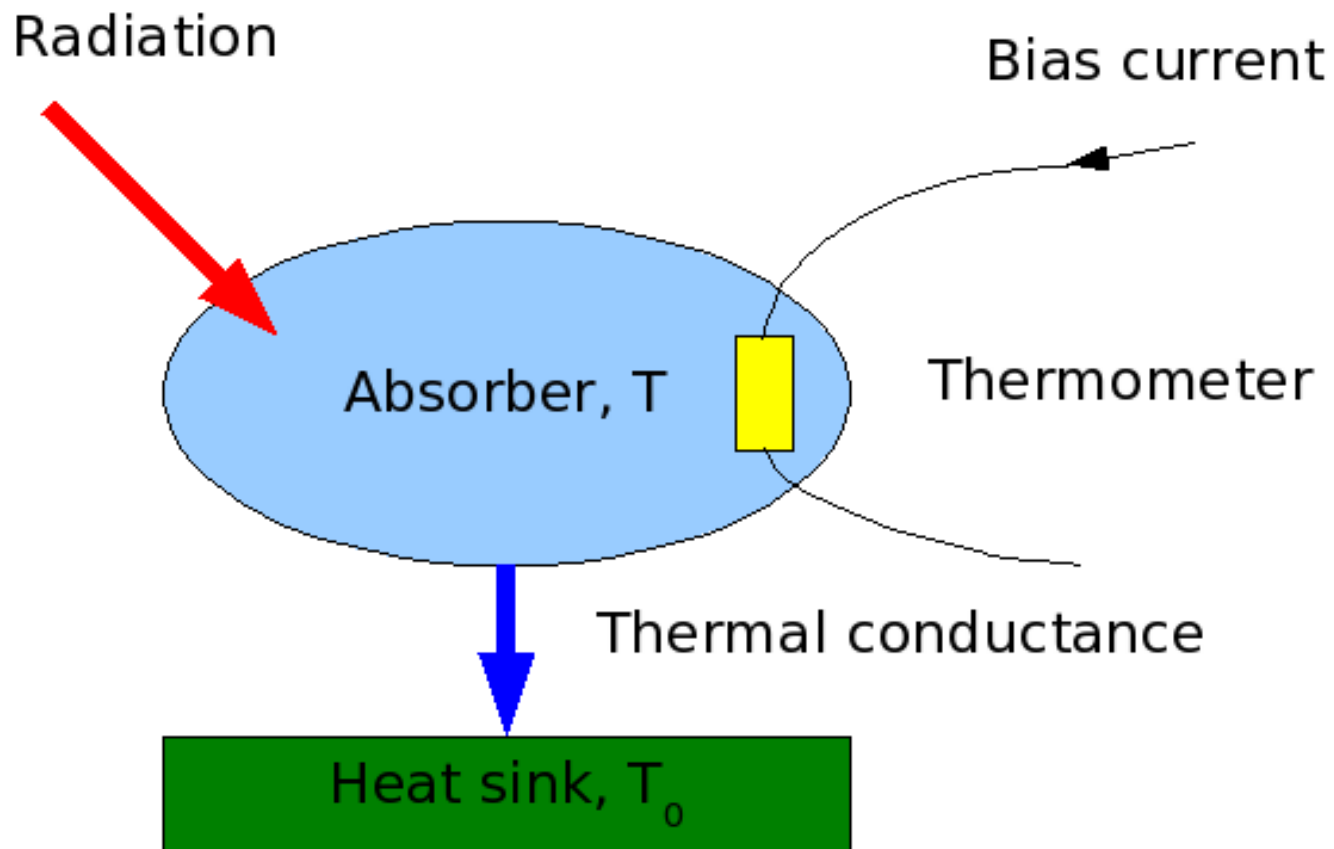
# Semi-conductor detectors

- See introduction on semiconductors in previous slides (conduction/valence bands)
- Gamma-ray interaction produces secondary electrons; they produce electron-hole pairs in the conduction/valence bands
- Electric field separates the pairs before recombination, drifting electrons to anode and holes to cathode. Charge is collected, which is proportional to energy deposited in detector
- Energy required to generate electron-hole pair is  $\epsilon=(14/5)E_g+c$ , where  $0.5\leq c\leq eV$
- Common detectors made of Ge (e.g., Integral SPI;  $E_g=0.74$  eV,  $\epsilon=2.98$  eV), Si ( $\epsilon=3.61$  eV), CdTe (Integral ISGRI;  $E_g=1.6$ eV,  $\epsilon=4.43$  eV)

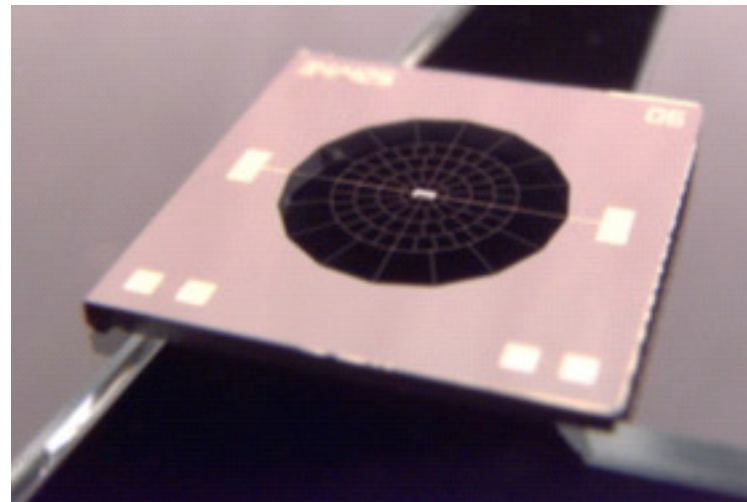
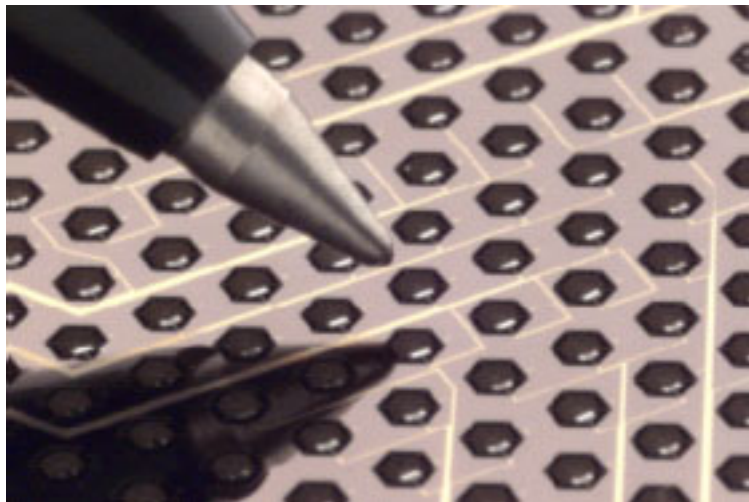
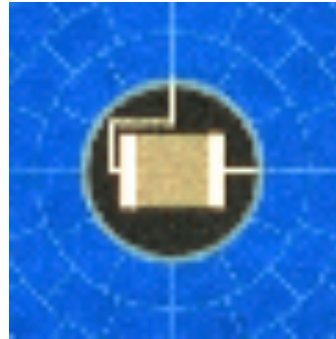
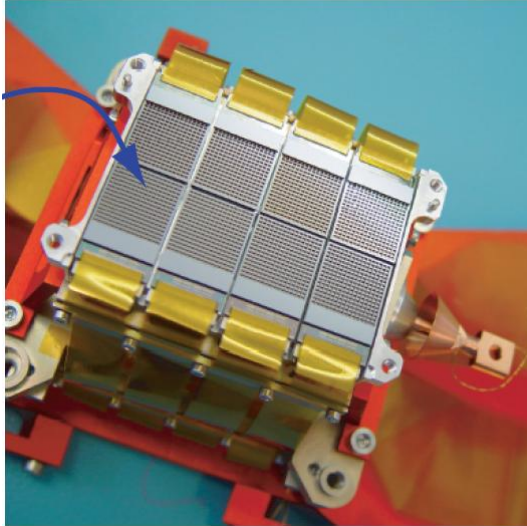
# Bolometer principles

- Sensitive to energy
- Not sensitive to ‘color’
- Suited for almost ANY wavelength
- Particularly suited for IR and FIR to sub-mm  
(but cooling to mK required)

# Bolometer principles

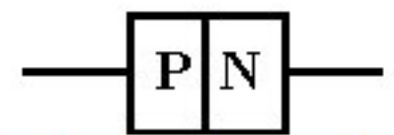
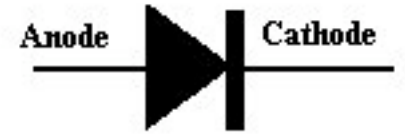
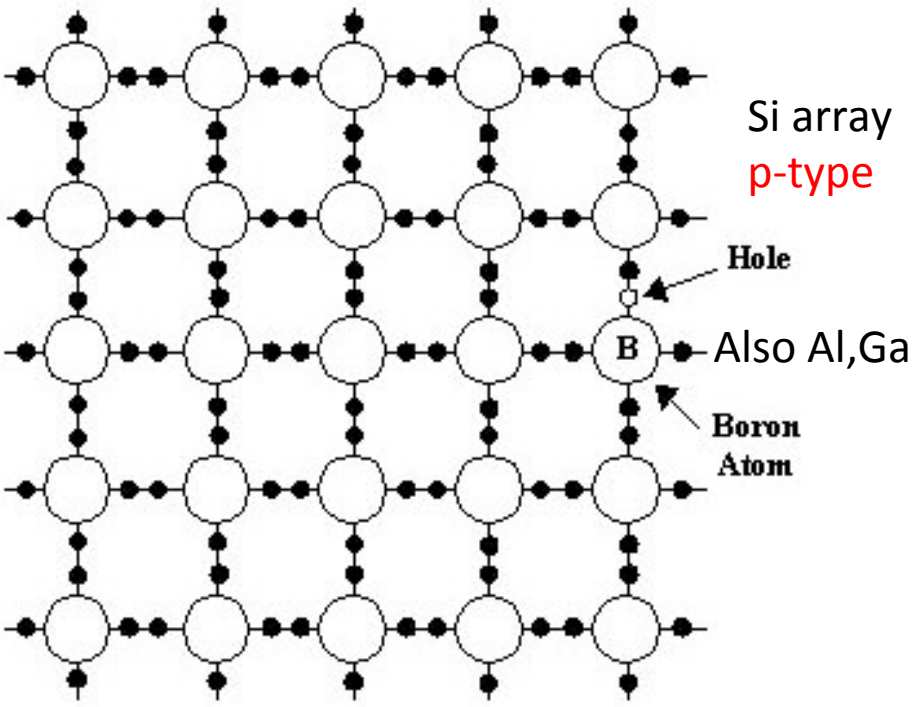
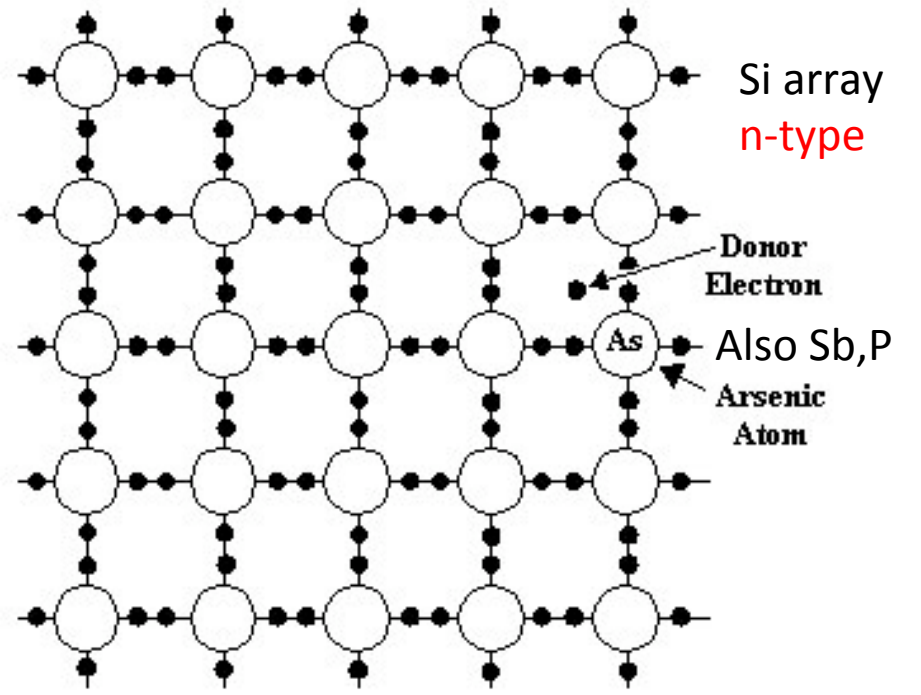
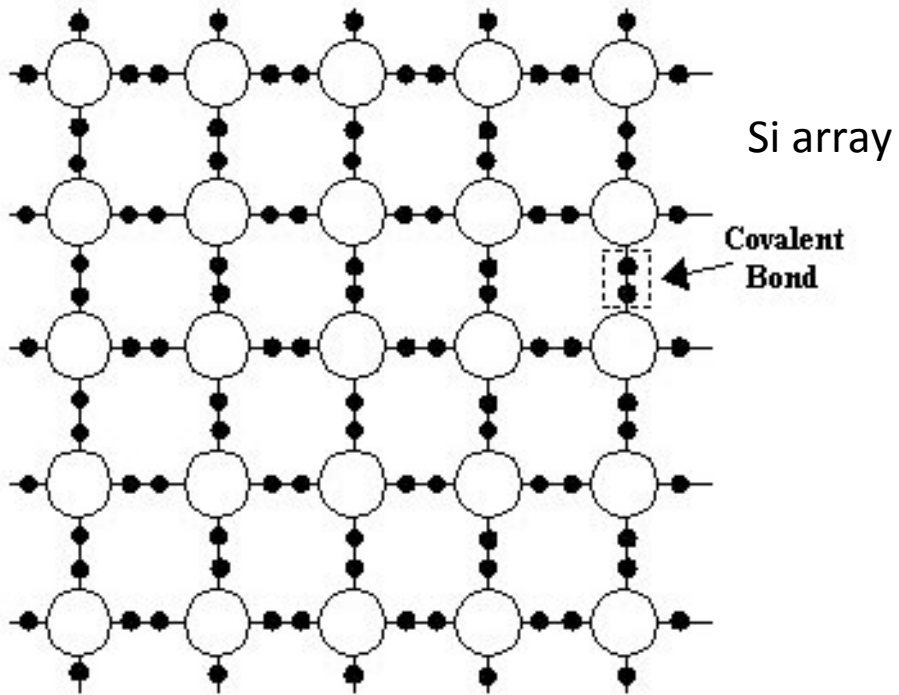


# Bolometers



# CCDs

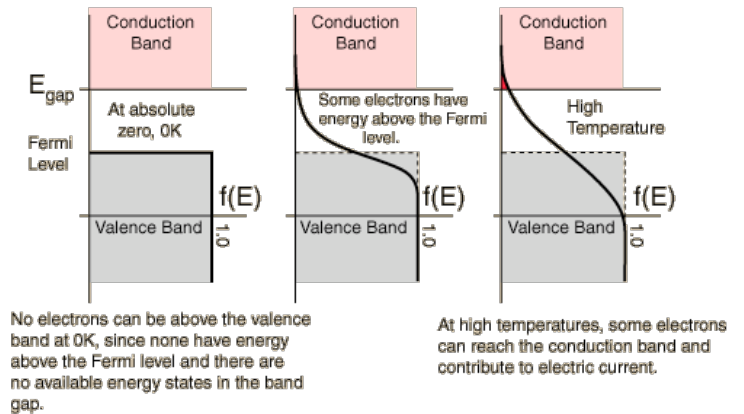
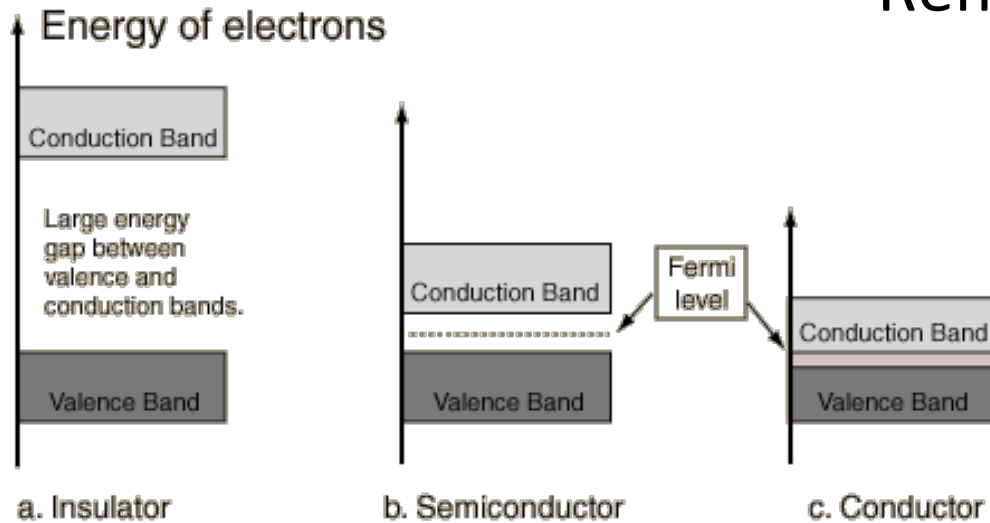
- Charge Coupled Devices invented in the 1970s
- Sensitive to light from optical to X-rays
- In practice, best use in optical and X-rays
- CCDs make use of silicon chips
- The CCD consists of (1) a p-type doped silicon substrate, (2) the charge storage (depletion) layer, which is covered by (3) a SiO<sub>2</sub> insulating layer; upon this is (4) an array of closely spaced electrodes, which can be set to pre-defined voltage value



The PN junction as a Diode



# Reminder of solid state physics

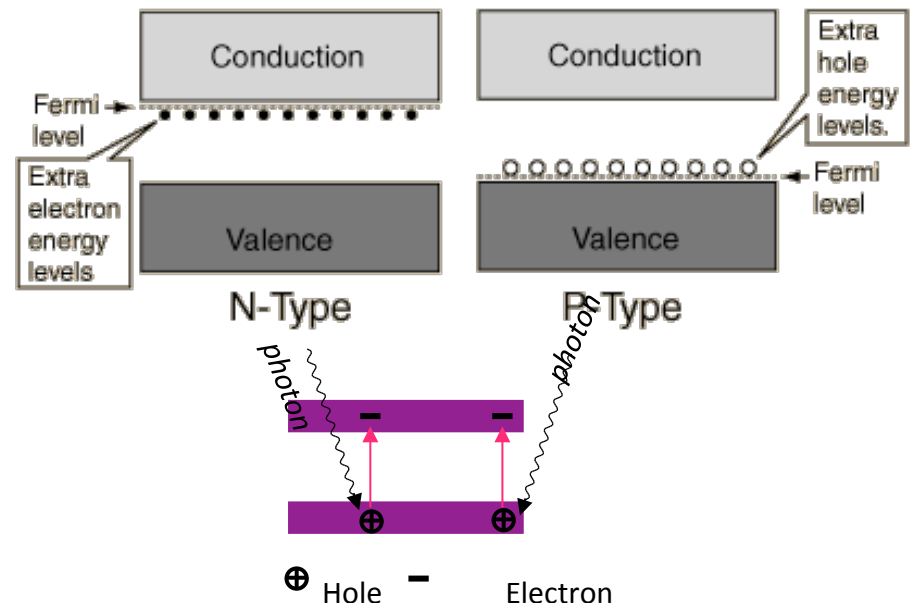


Electrons in a lattice do not have discrete energies. They form energy bands:

- Valence band
- Conduction band

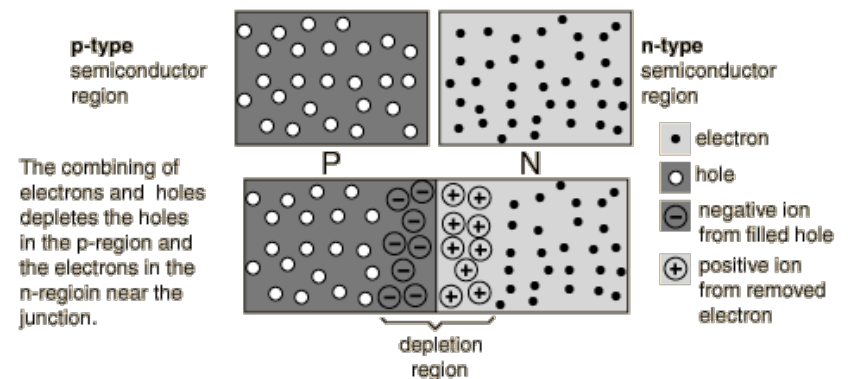
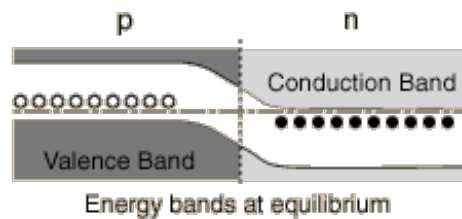
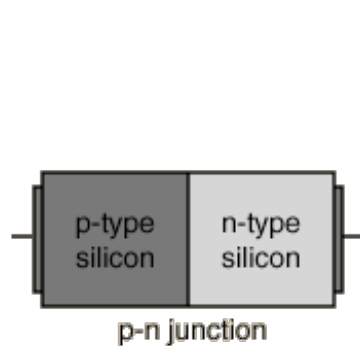
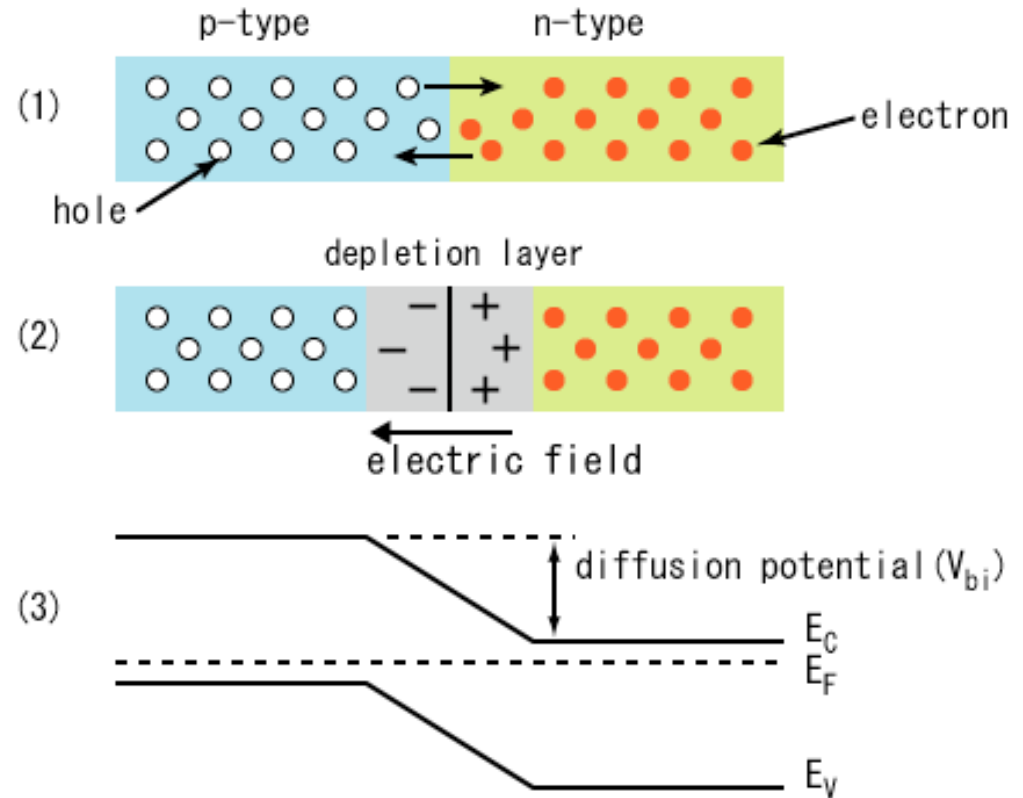
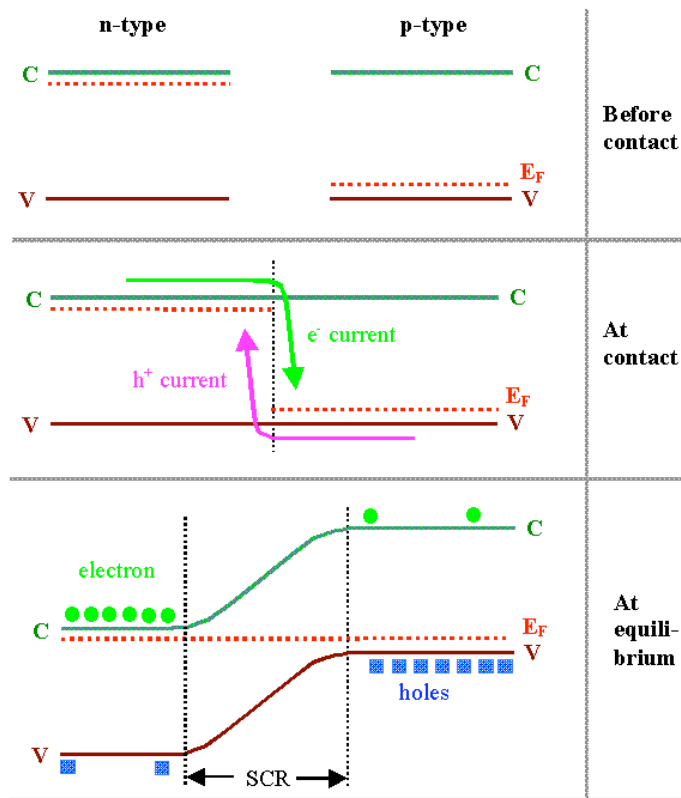
For semi-conductors, the Fermi level is just in the middle of the conduction and valence bands. At finite temperature, some electrons of the valence band can jump into the conduction band (current noise)

$E_G(\text{Si})=1.1 \text{ eV}$  (IR),  $E_G(\text{Ge})=0.72 \text{ eV}$   
 $E_G(\text{C})=5.5 \text{ eV}$  (insulator)

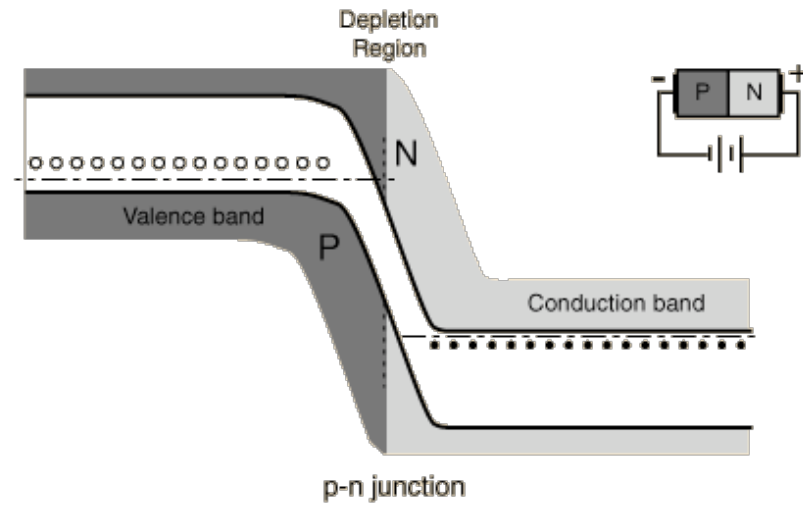
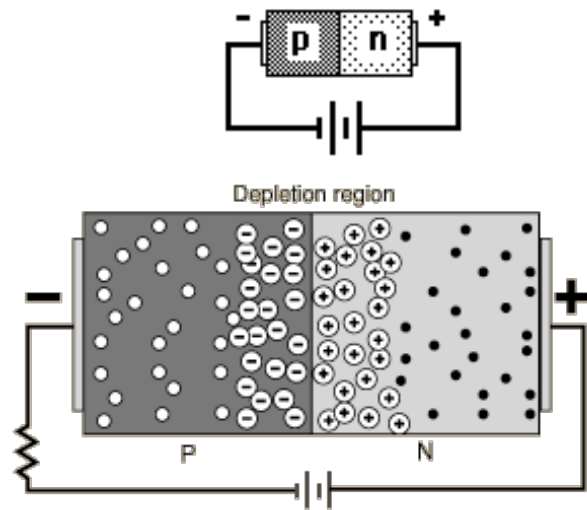


(From <http://hyperphysics.phy-astr.gsu.edu/hbase/hframe.html>)

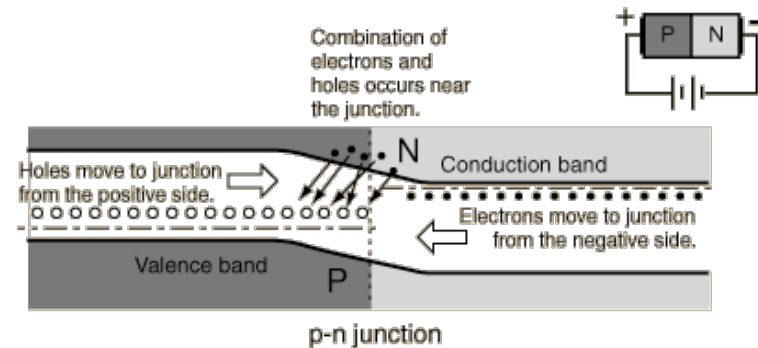
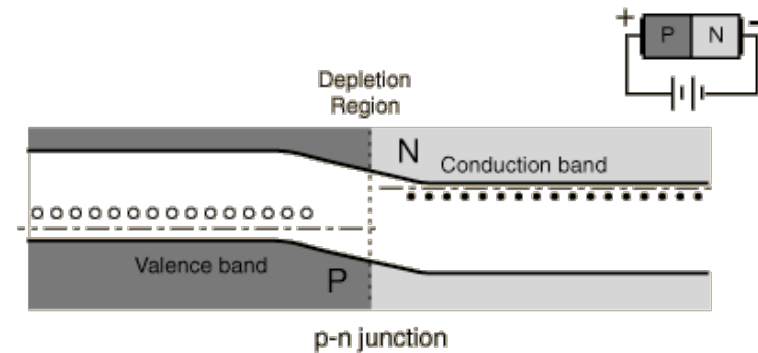
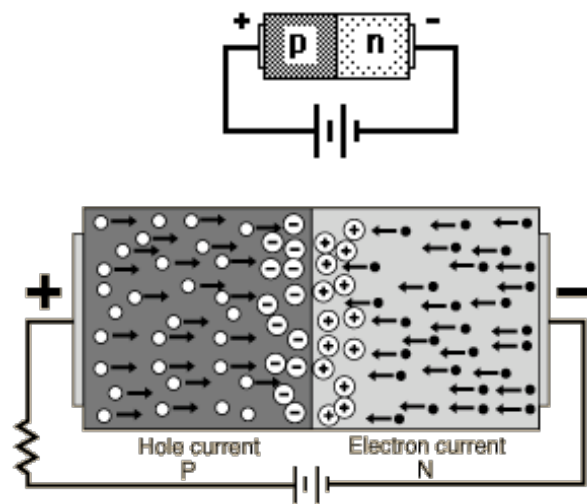
# The pn junction



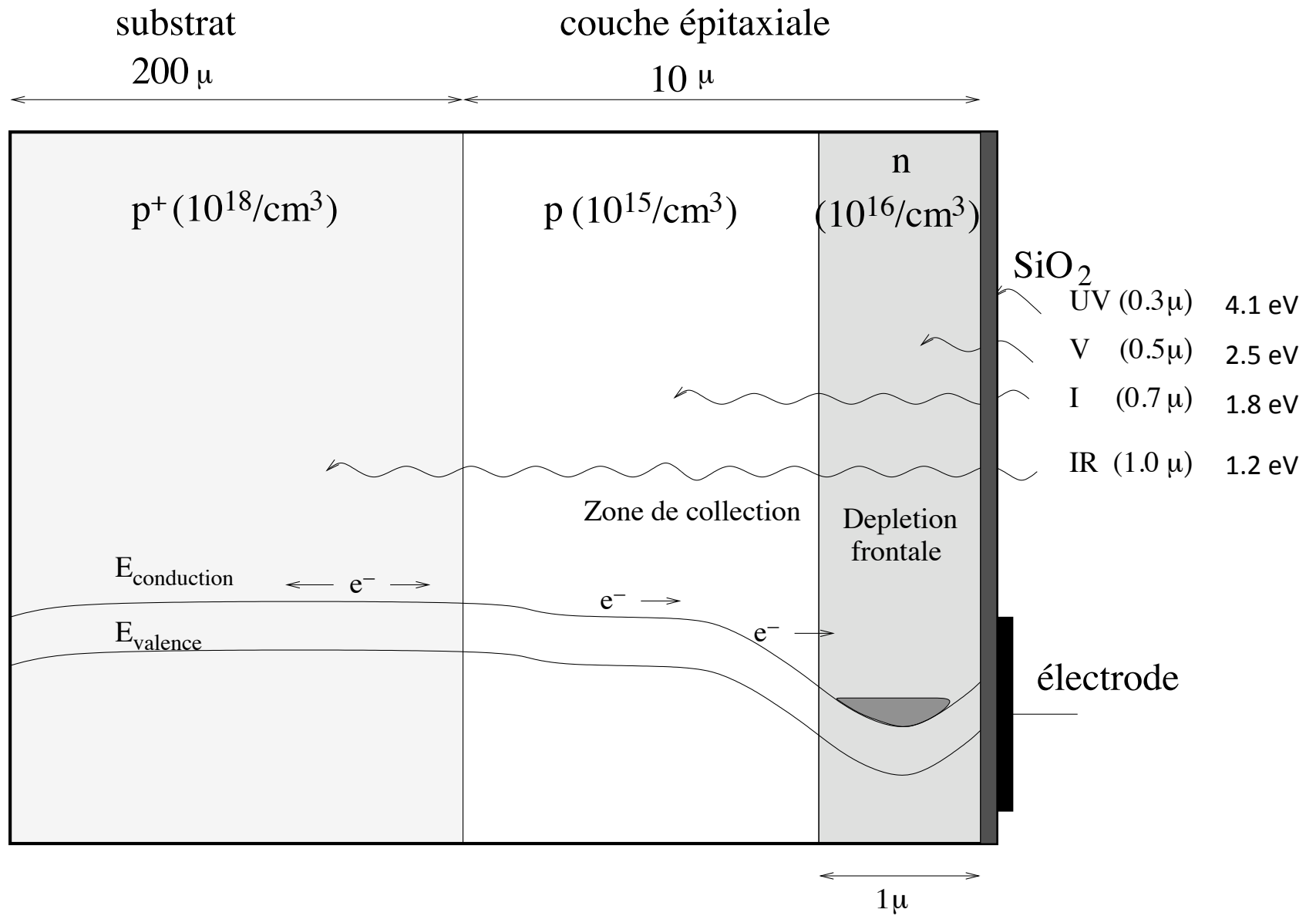
## Reverse-biased pn junction



## Forward-biased pn junction



- Electron
- Hole
- ⊖ Negative ion from filling of p-type vacancy.
- ⊕ Positive ion from removal of electron from n-type impurity.



Blecha (cours instrumentation)

Transverse cut of CCD with buried channel

## Metal Oxide Semiconductor (MOS) Capacitor

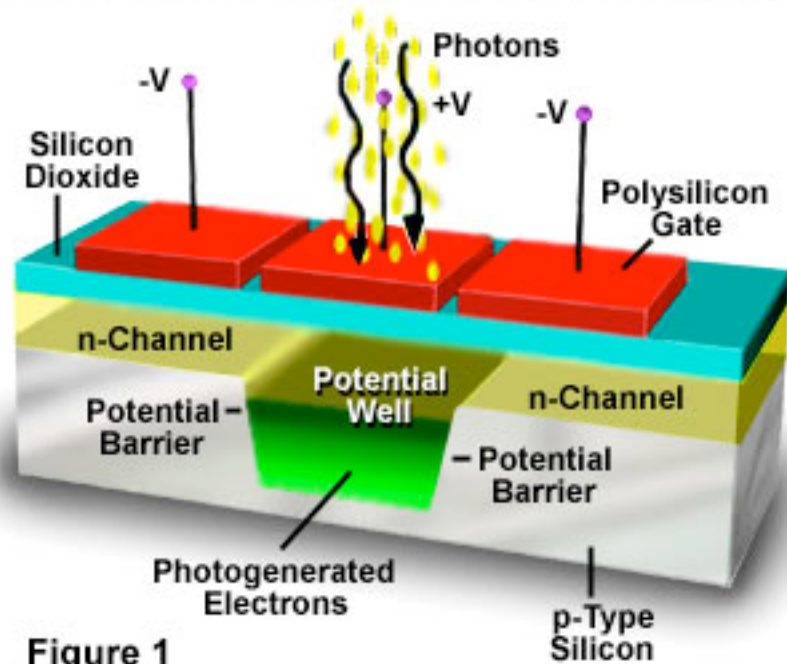
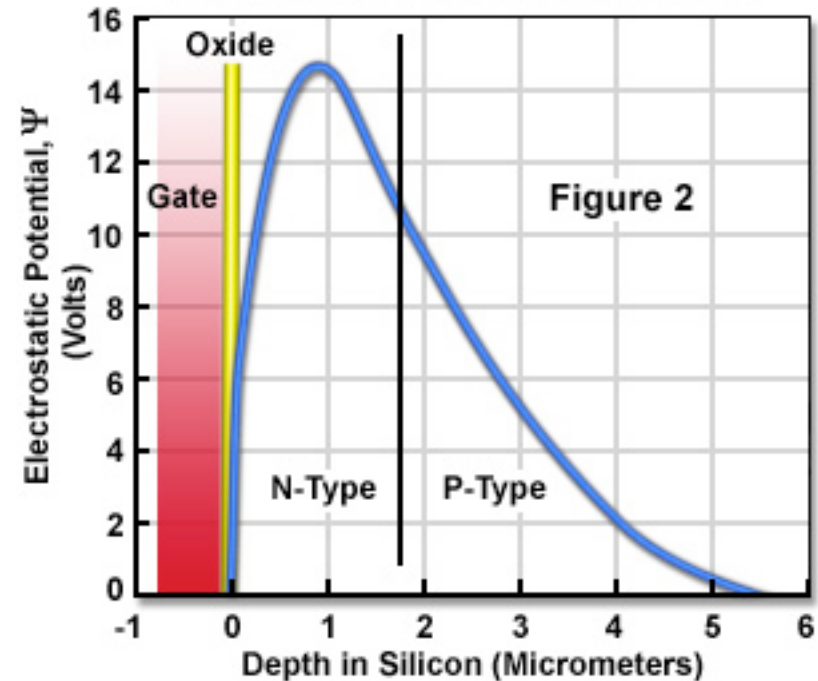


Figure 1

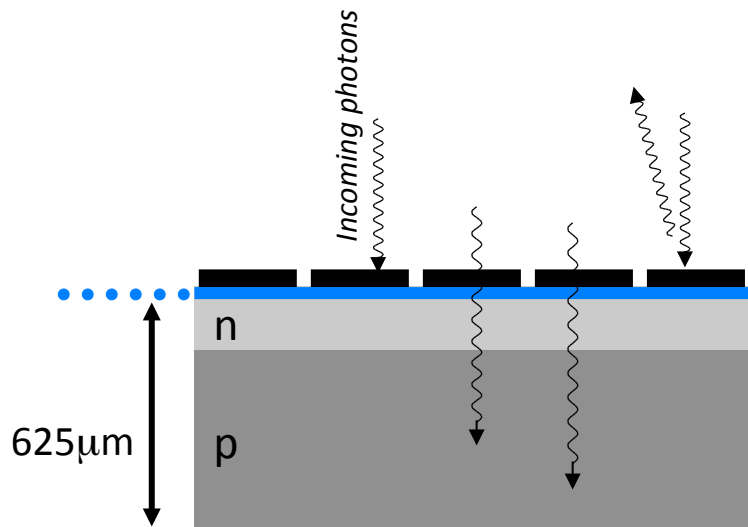
The electrode has positive potential to attract the generated photoelectrons in a potential well

The above MOS capacitor is 1 pixel

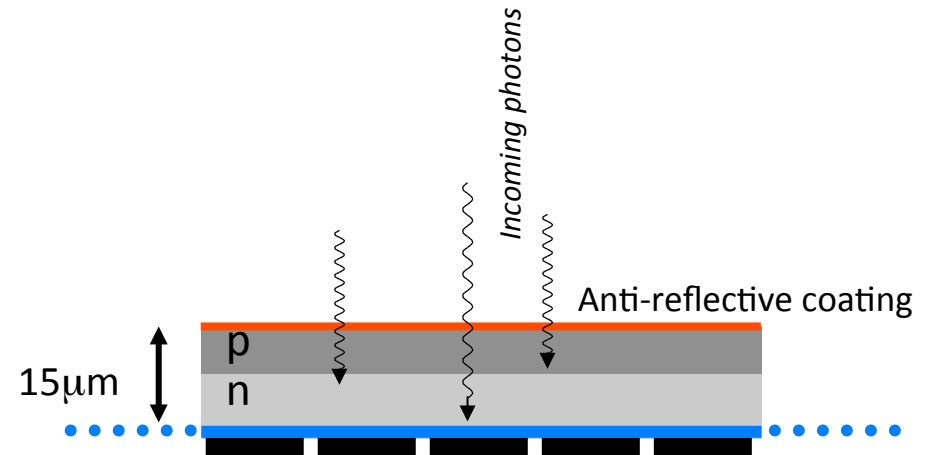
## Electron Distribution in Buried Channel MOS Capacitors



## Front-illuminated CCDs



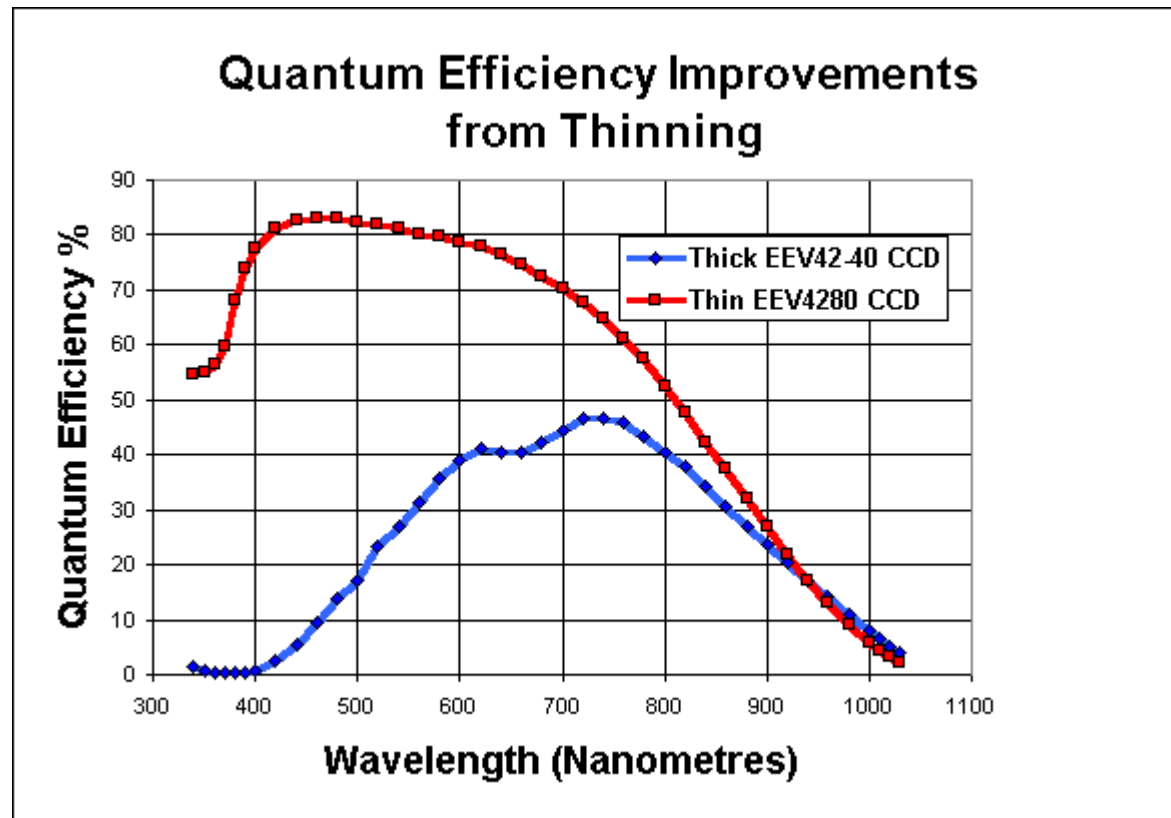
They have a low Quantum Efficiency due to the reflection and absorption of light in the surface electrodes. Very poor blue response. The electrode structure prevents the use of an anti-reflective coating that would otherwise boost performance.



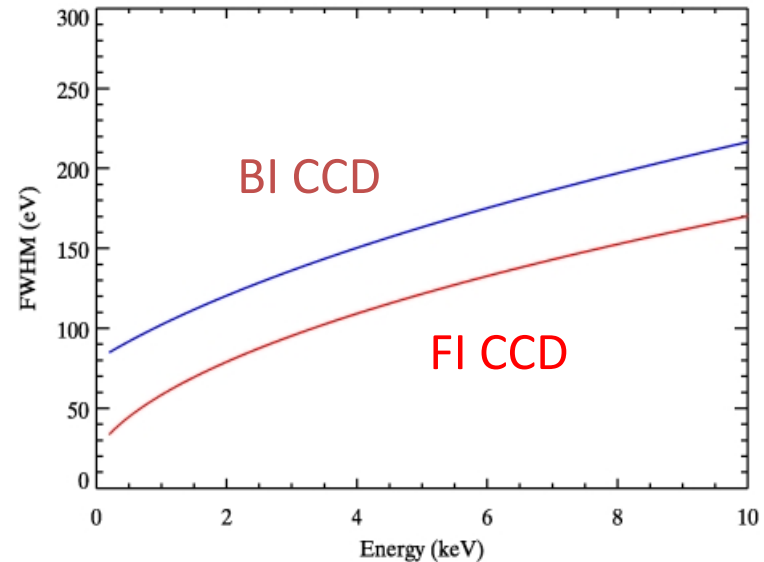
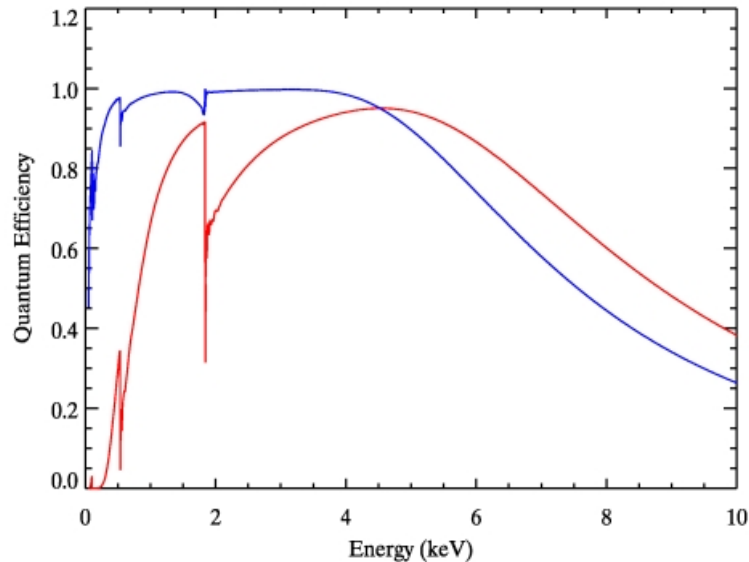
The QE can approach 100% . These thinned CCDs become transparent to near infra-red light and the red response is poor. Response can be boosted by the application of an anti-reflective coating on the thinned rear-side. These coatings do not work so well for front-illuminated CCDs due to the surface bumps created by the surface electrodes

## Quantum Efficiency Comparison

The graph below compares the quantum efficiency of a thick frontside illuminated CCD and a thin backside illuminated CCD.



# Back-illuminated CCDs

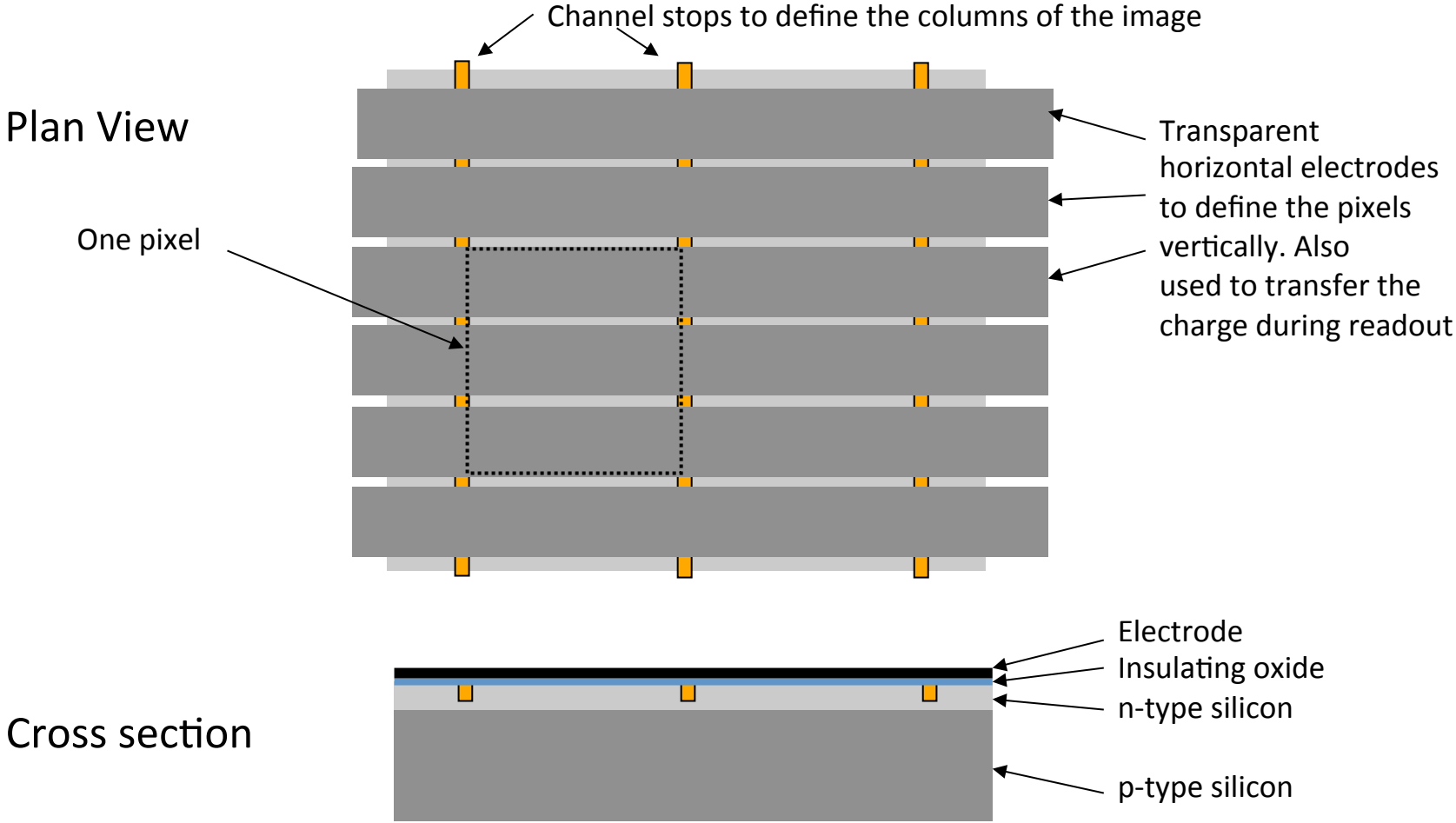


- Thinner deadlayers  $\Rightarrow$  higher low-E QE
- Thinner active region  $\Rightarrow$  lower high-E QE
- Increased noise, charge transfer inefficiency  $\Rightarrow$  higher FWHM



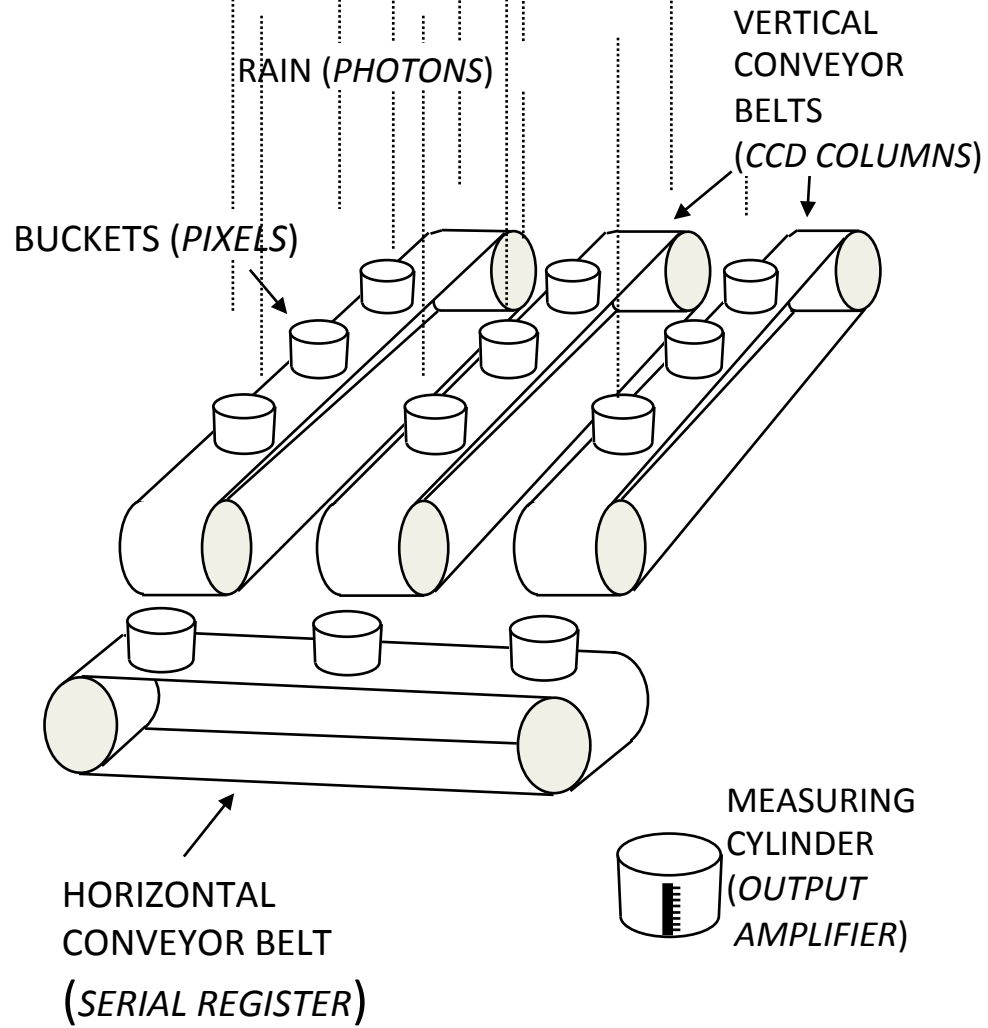
# Structure of a CCD

The diagram shows a small section (a few pixels) of the image area of a CCD. This pattern is repeated.

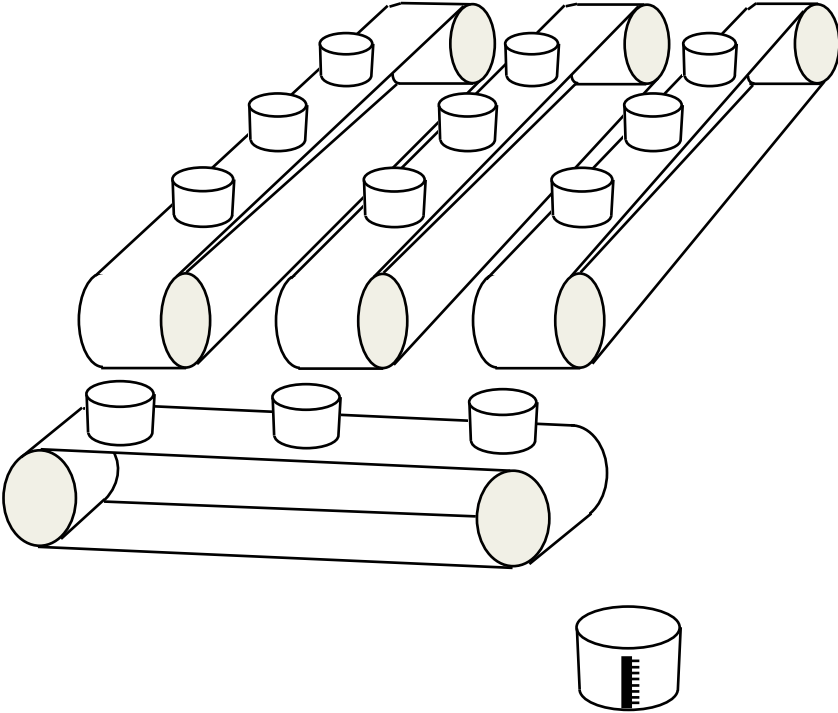


Every third electrode is connected together. Bus wires running down the edge of the chip make the connection. The channel stops are formed from high concentrations of Boron in the silicon.

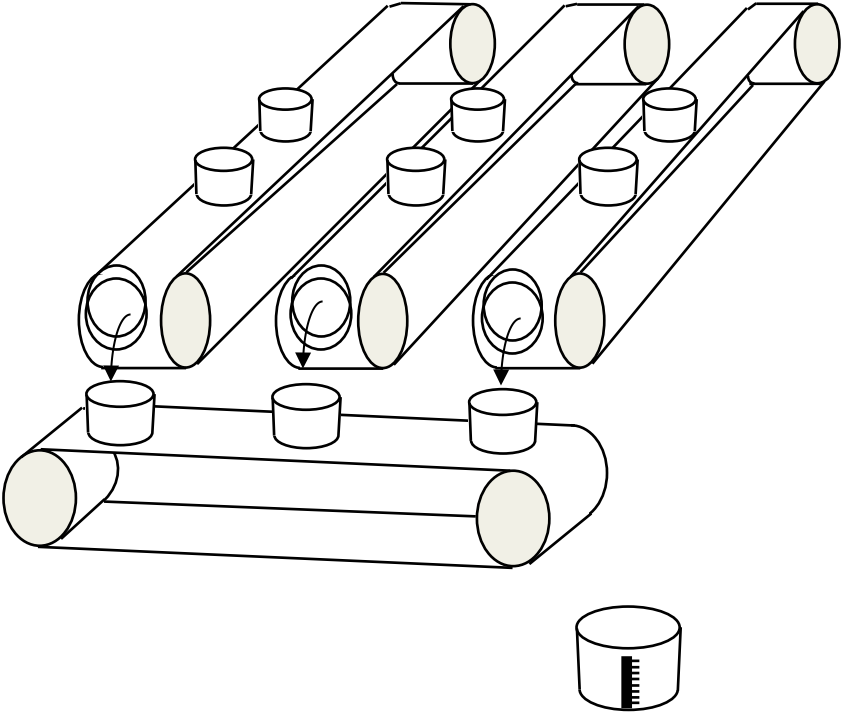
# CCD Analogy



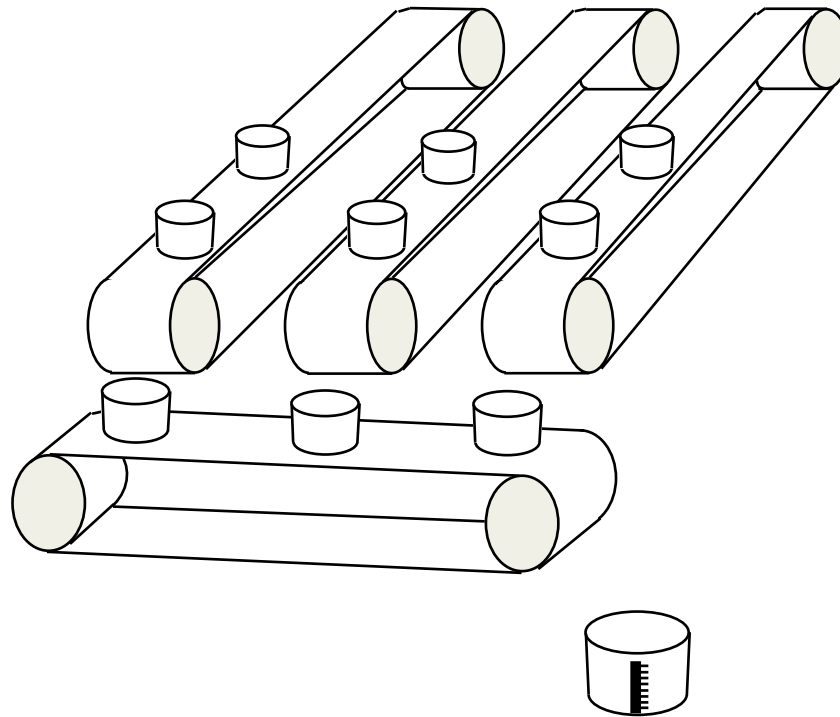
Exposure finished, buckets now contain samples of rain.



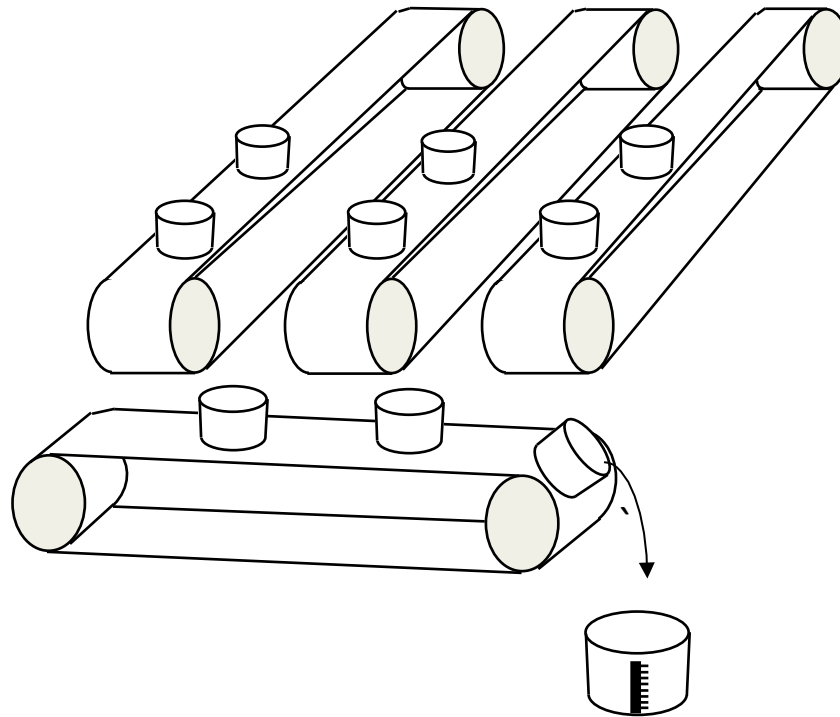
Conveyor belt starts turning and transfers buckets. Rain collected on the vertical conveyor is tipped into buckets on the horizontal conveyor.

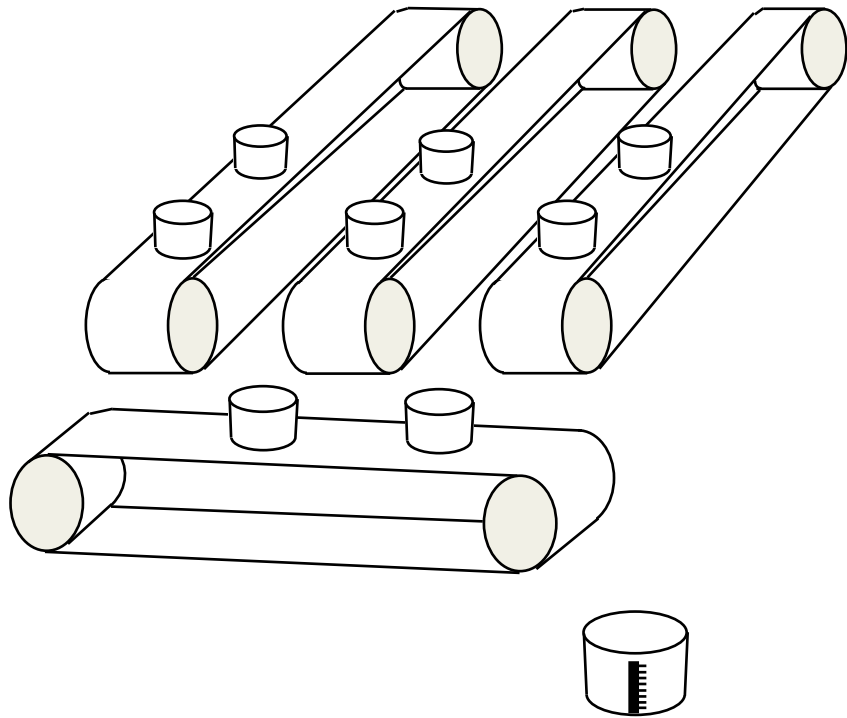


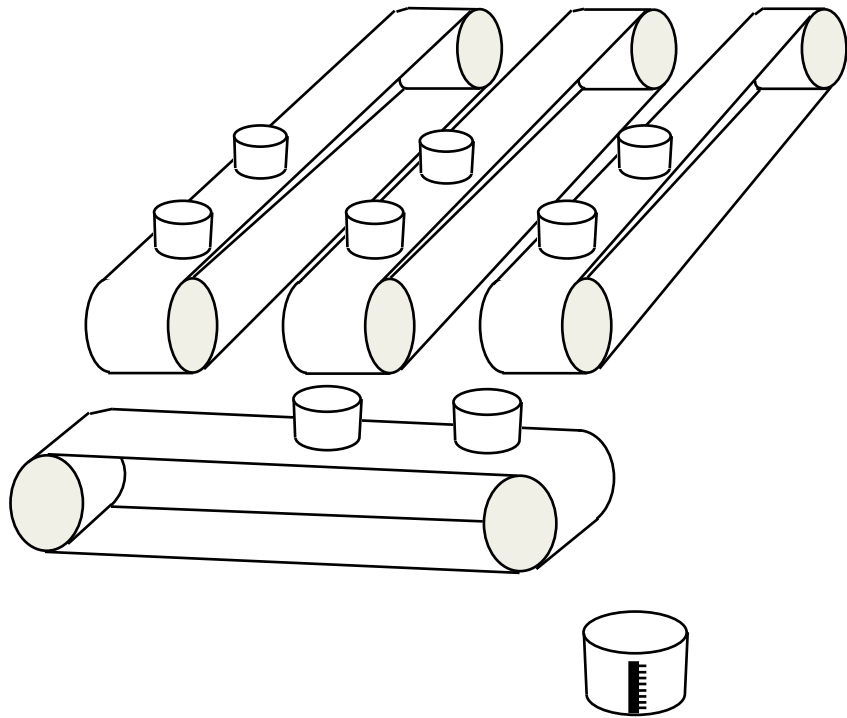
Vertical conveyor stops. Horizontal conveyor starts up and tips each bucket in turn into the measuring cylinder .



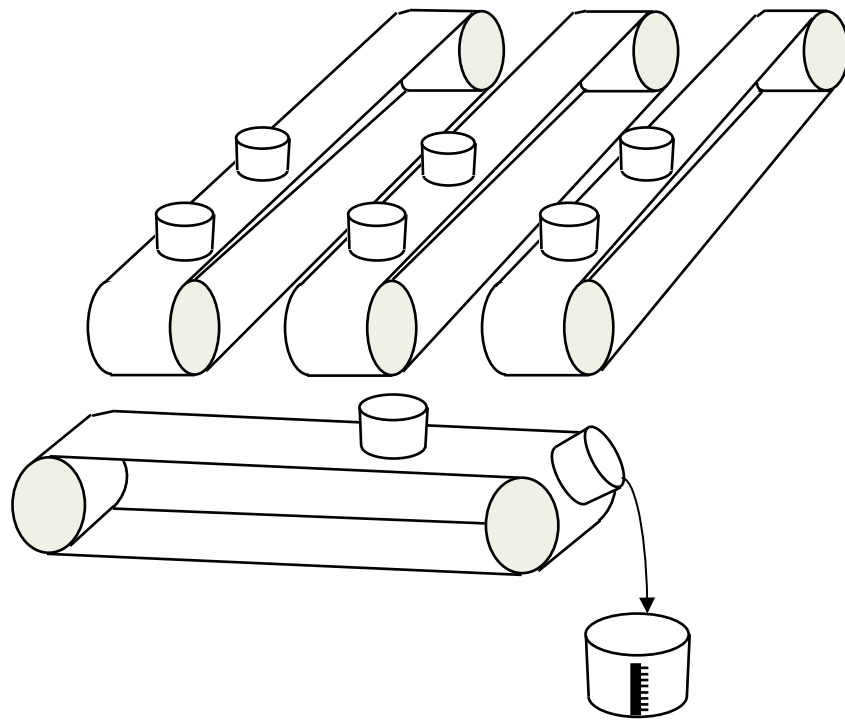
After each bucket has been measured, the measuring cylinder is emptied , ready for the next bucket load.

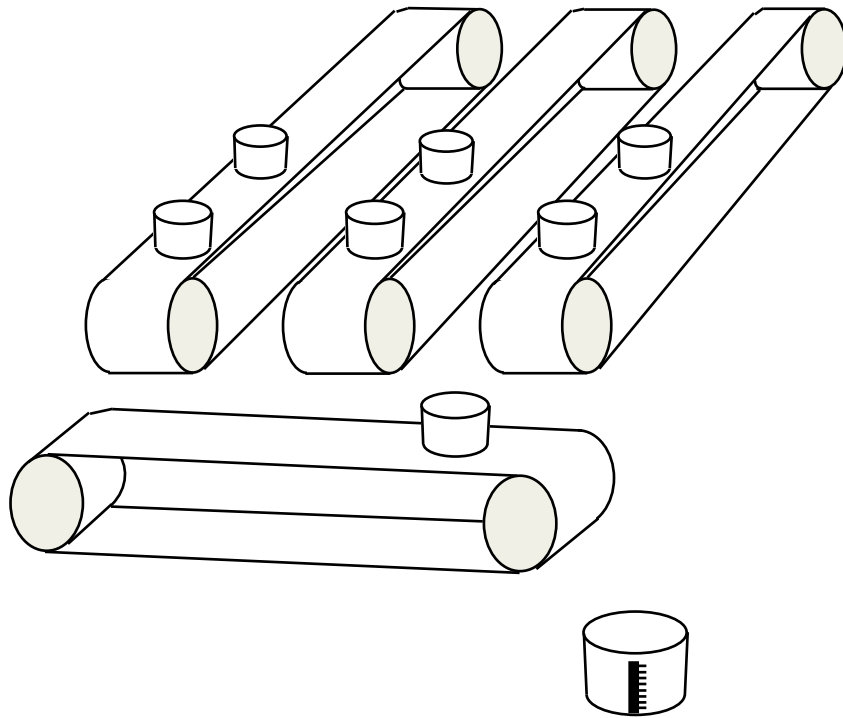


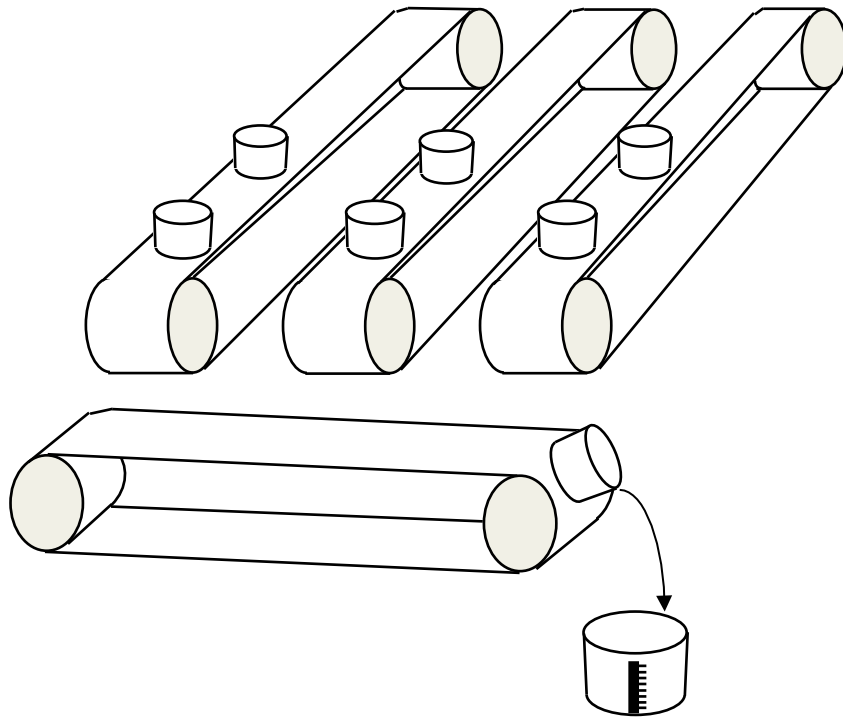


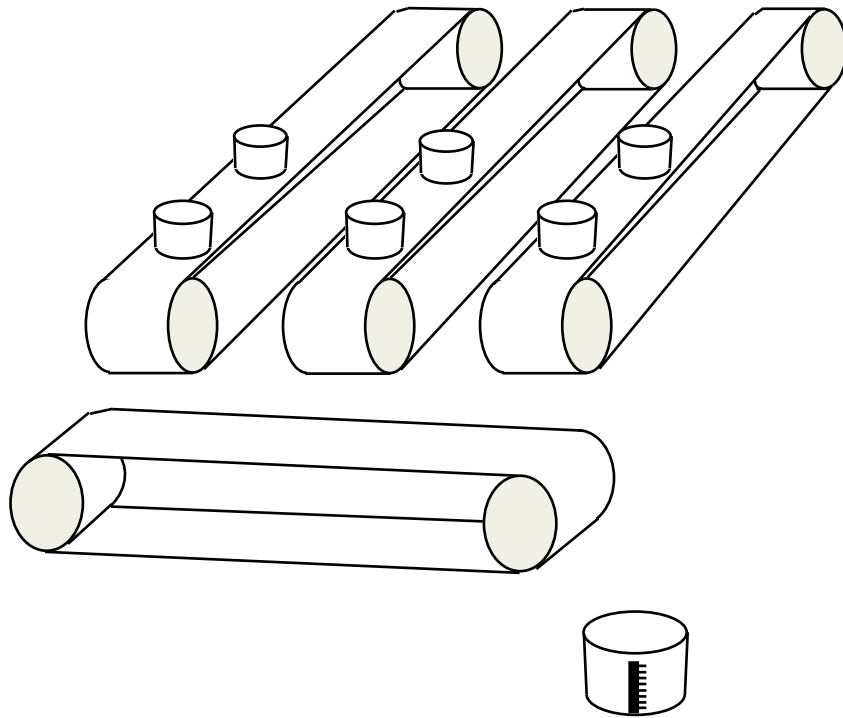




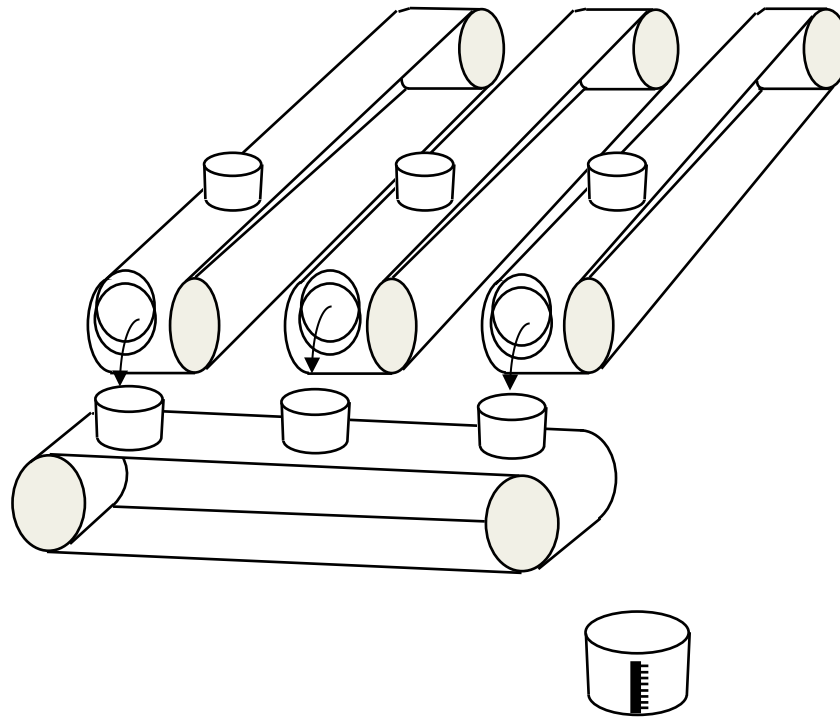


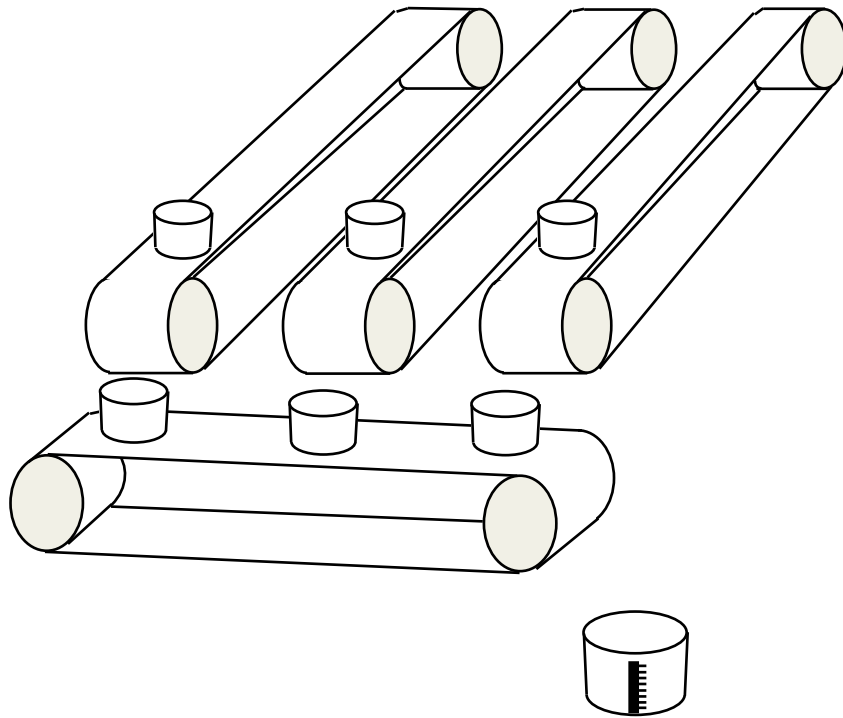


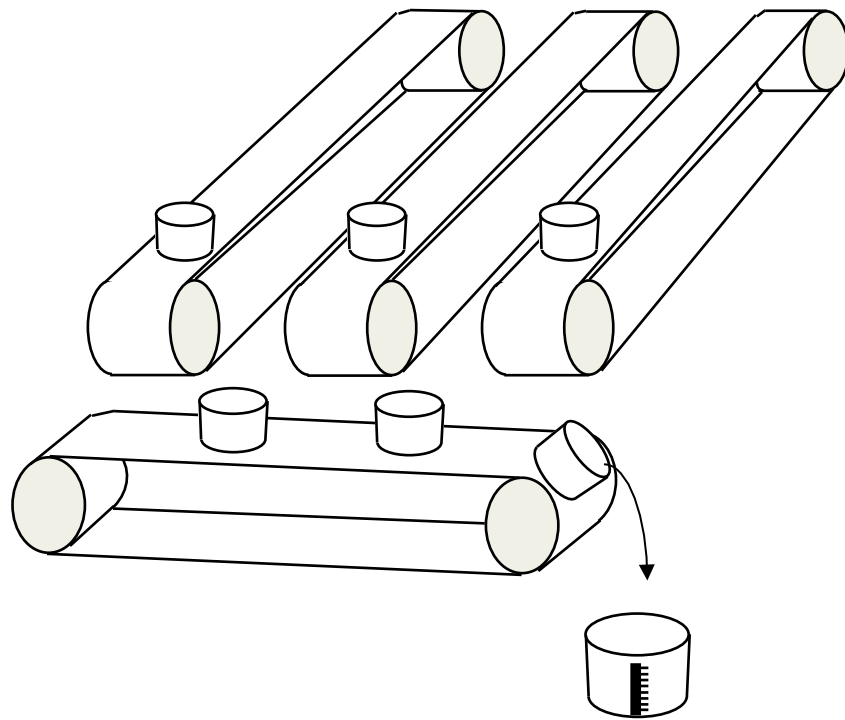


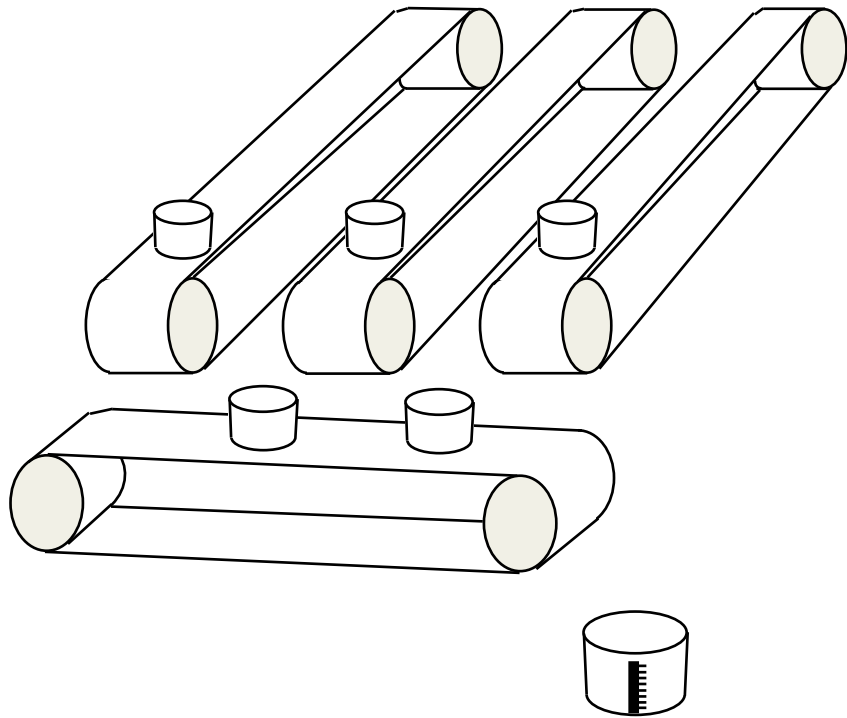


A new set of empty buckets is set up on the horizontal conveyor and the process is repeated.

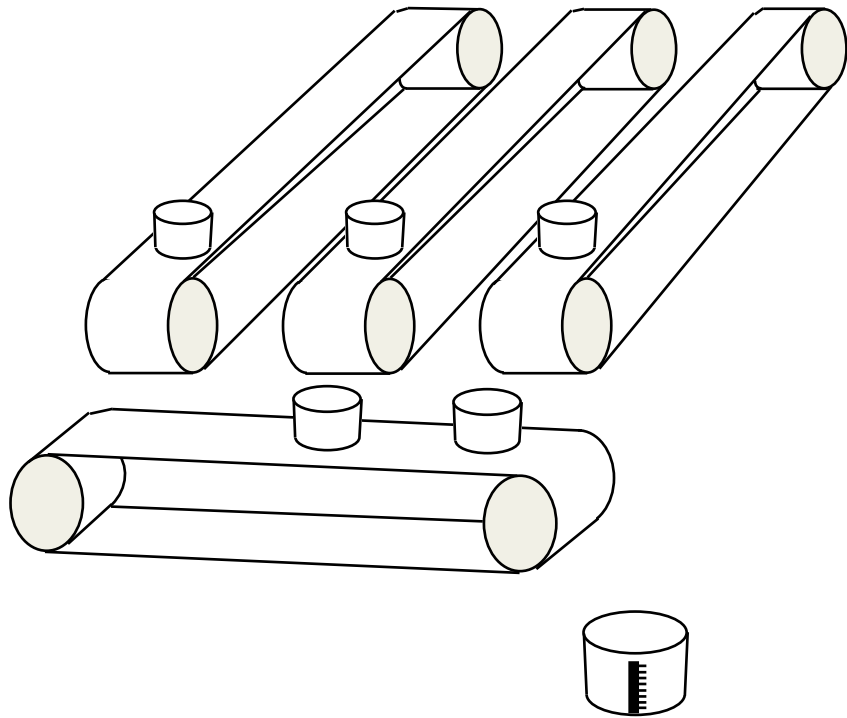


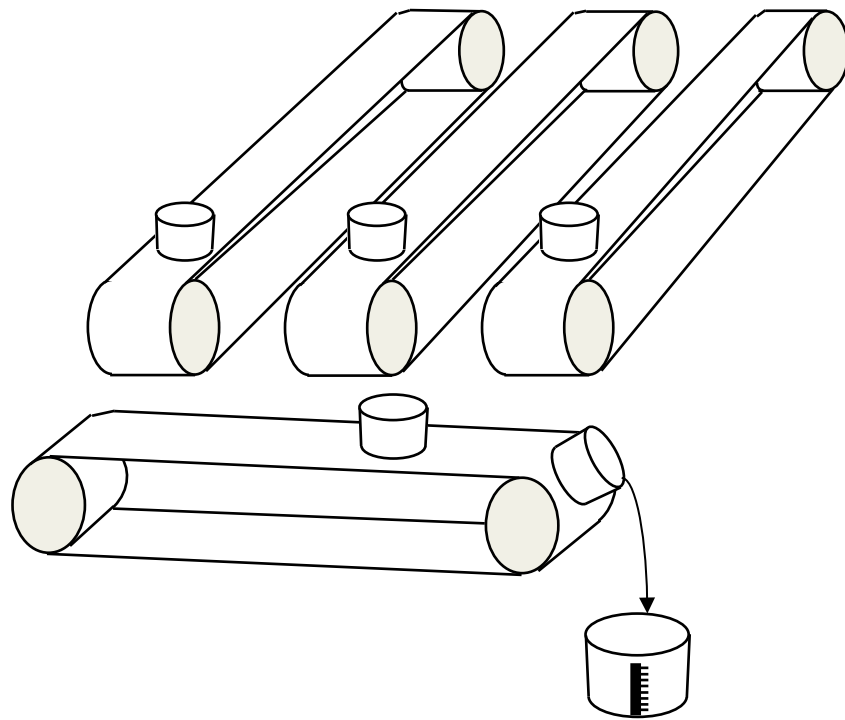




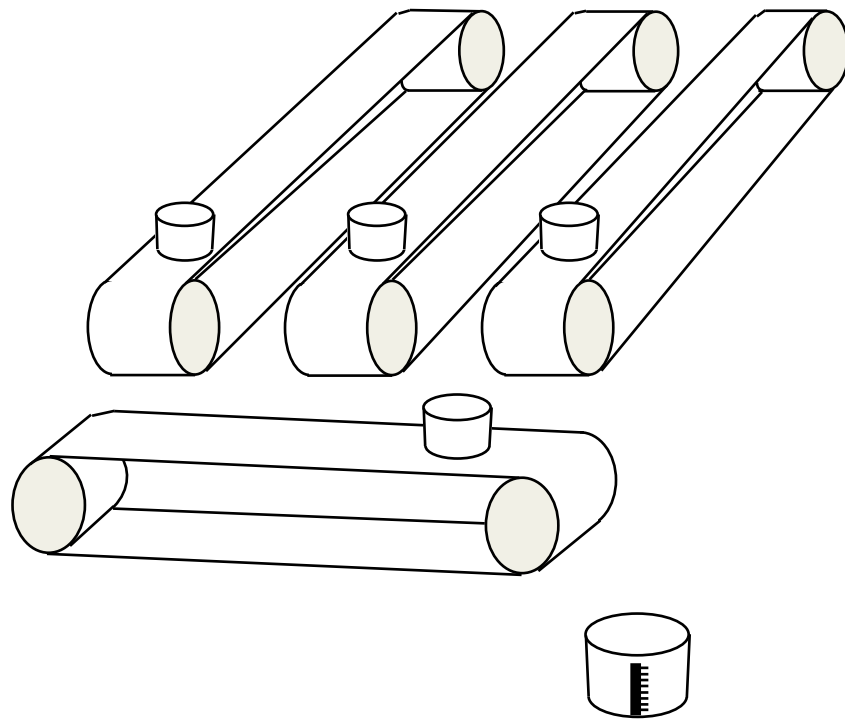




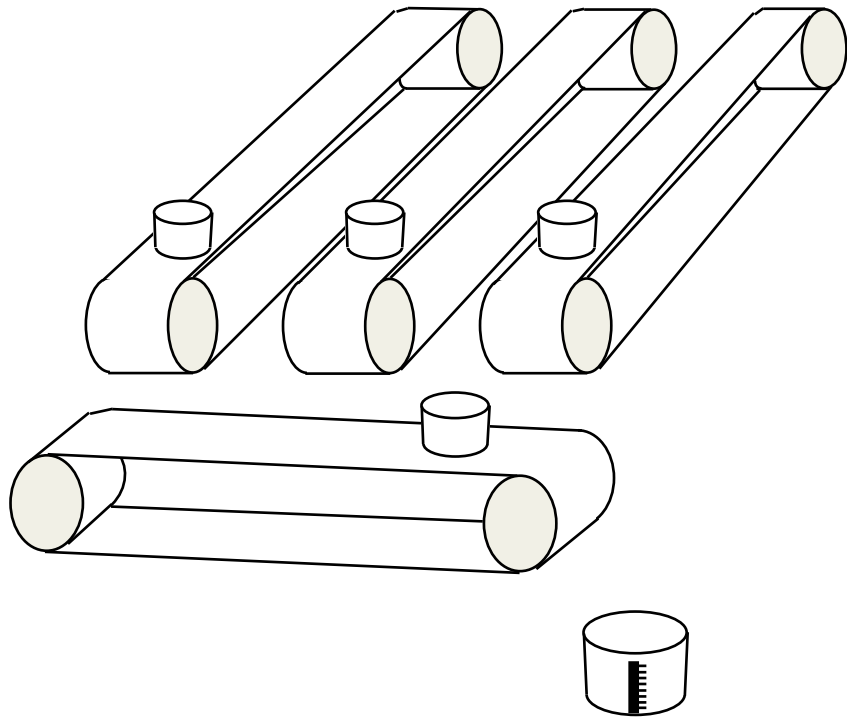


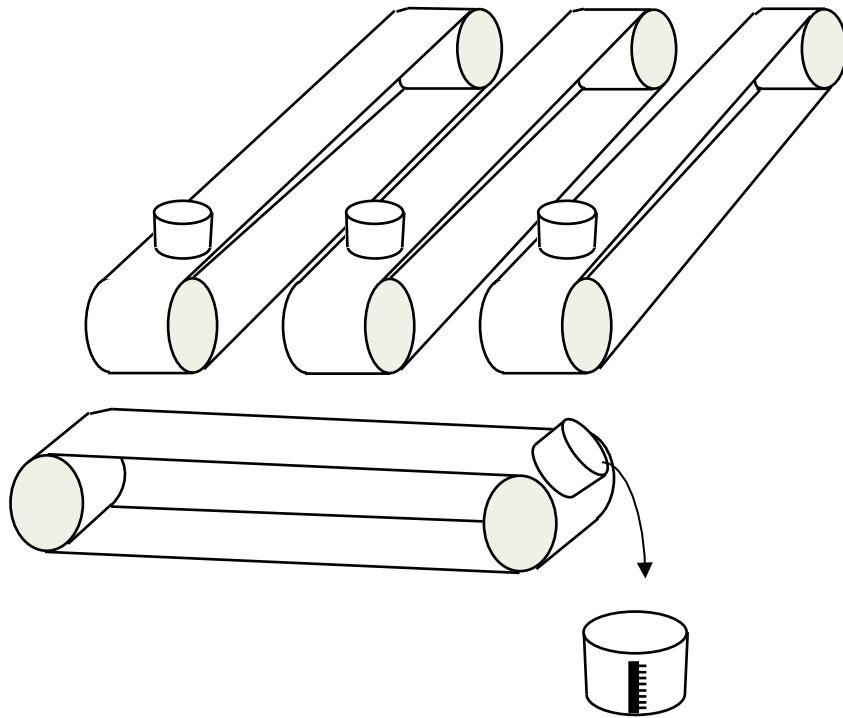


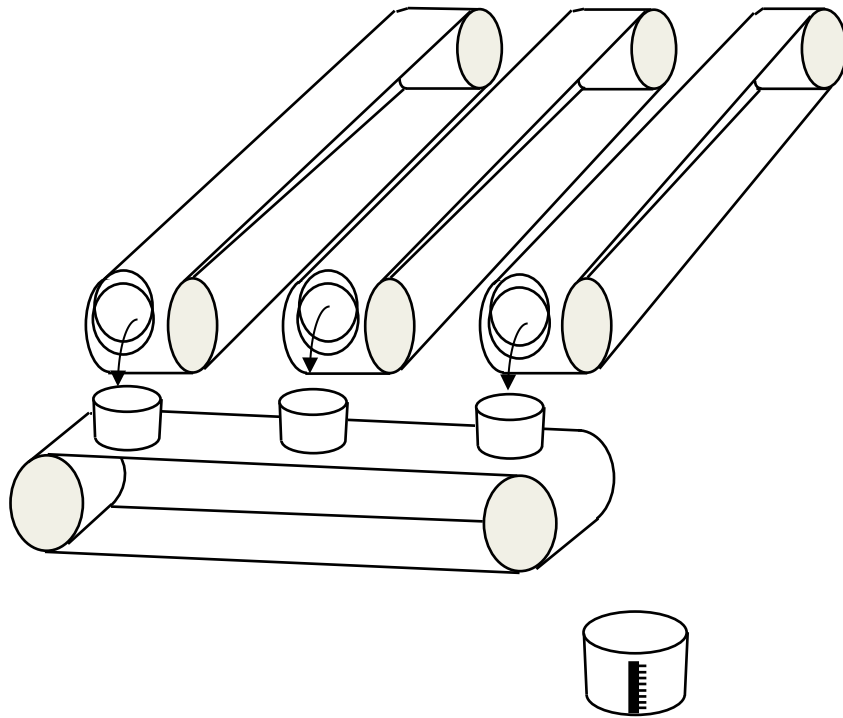
Courtesy of S. Tulloch

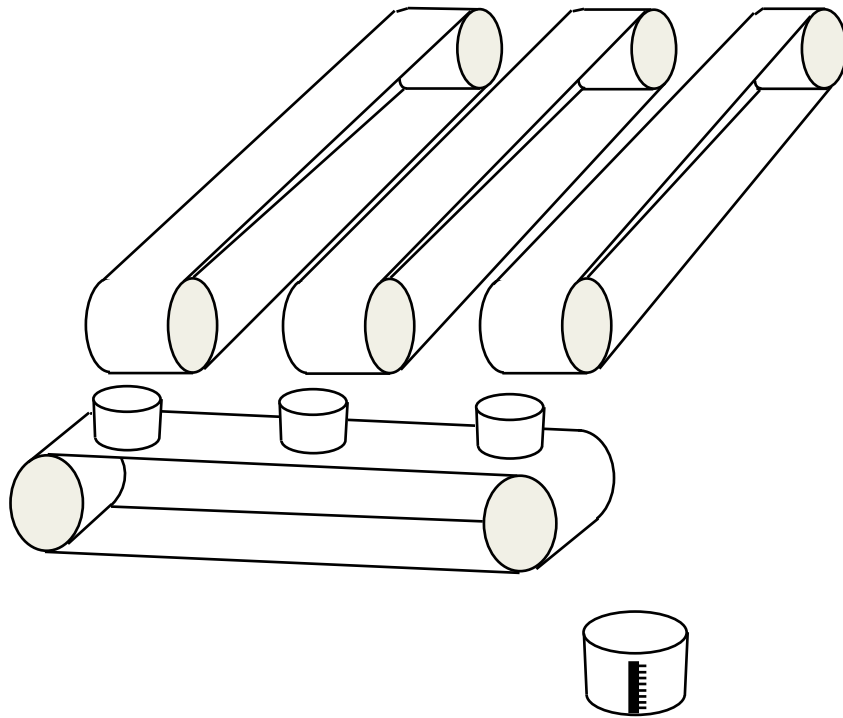


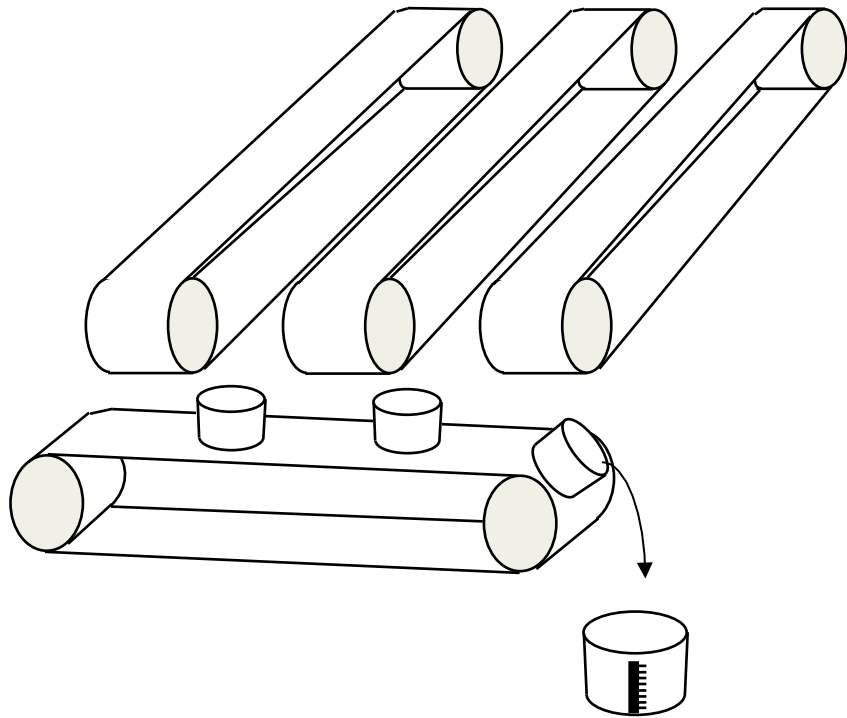
Courtesy of S. Tulloch



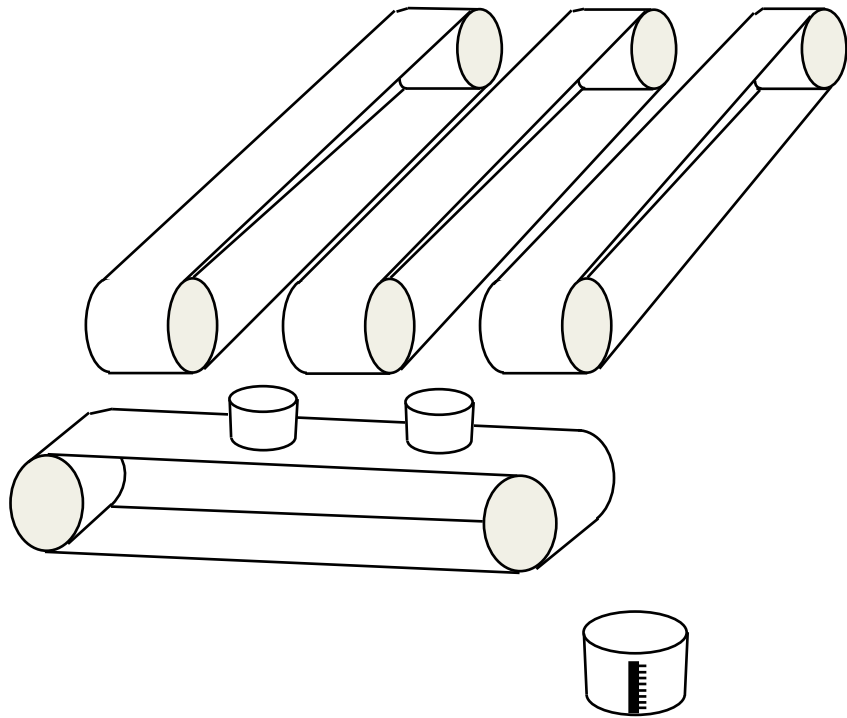


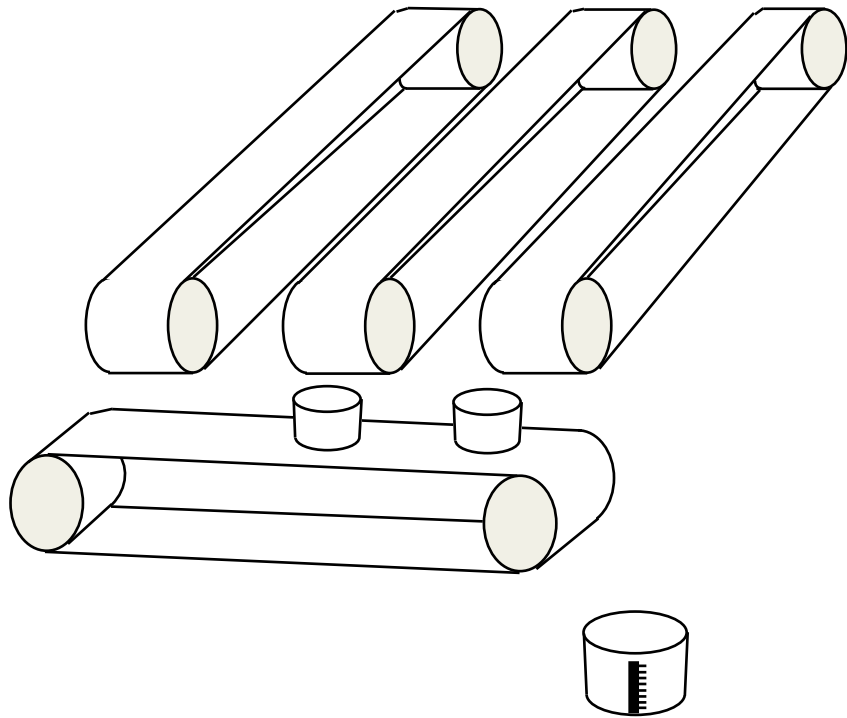


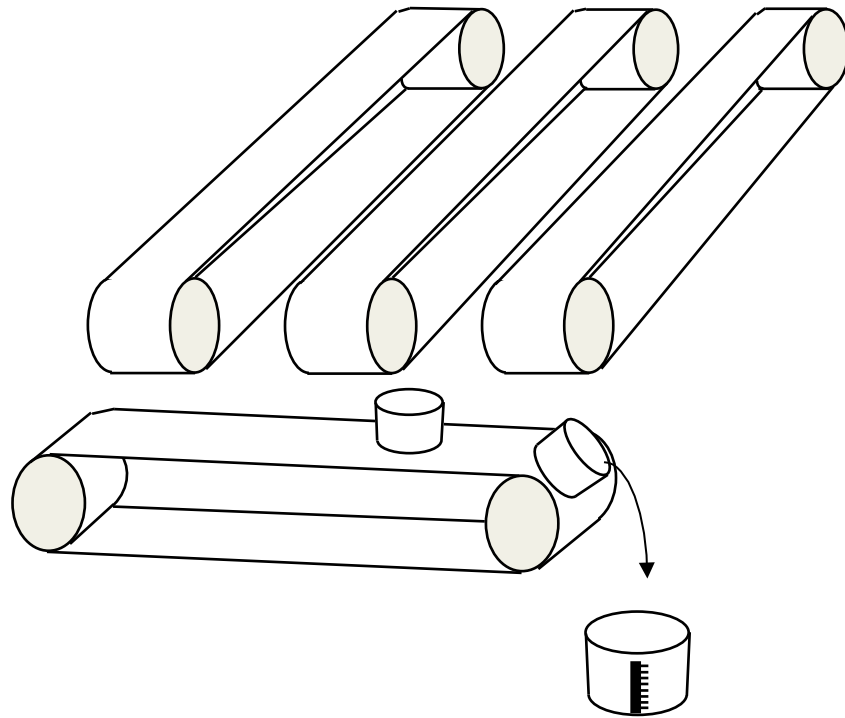


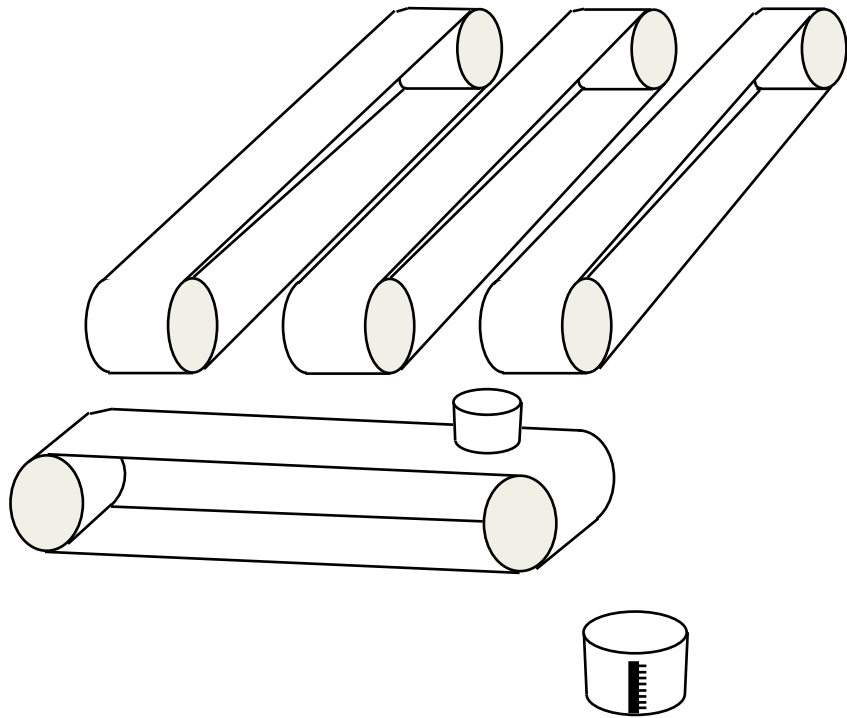


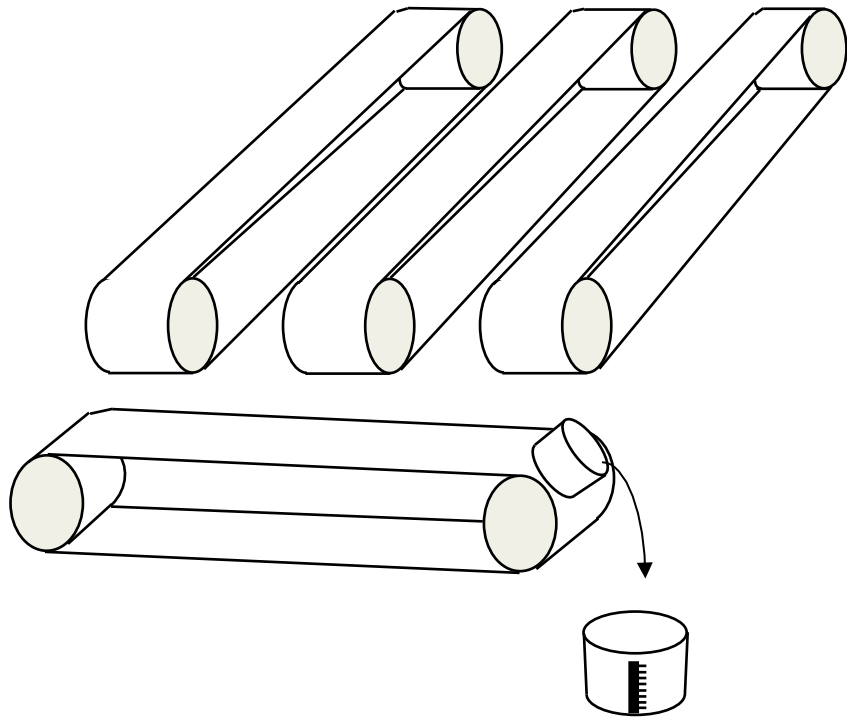




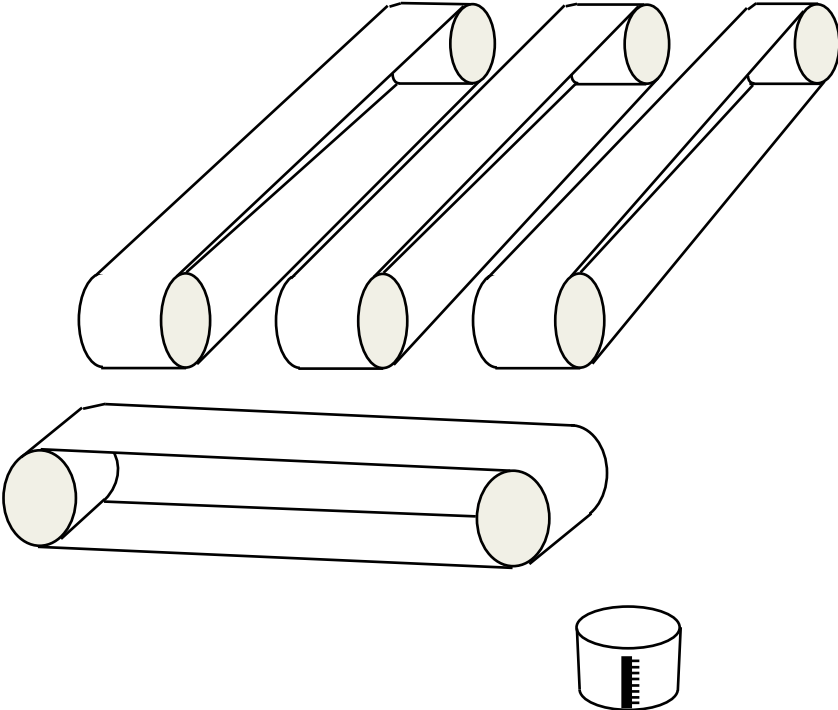






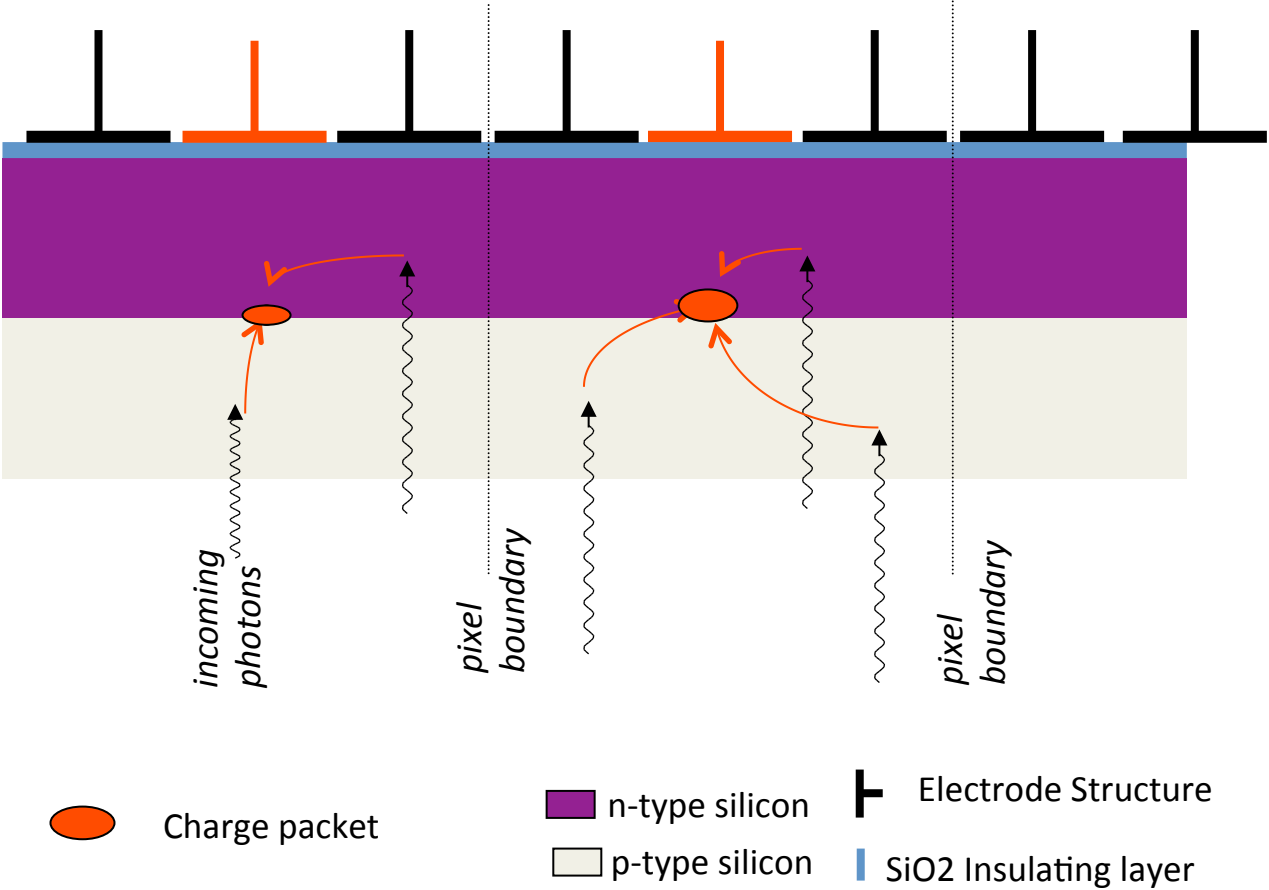


Eventually all the buckets have been measured, the CCD has been read out.



# Charge Collection in a CCD.

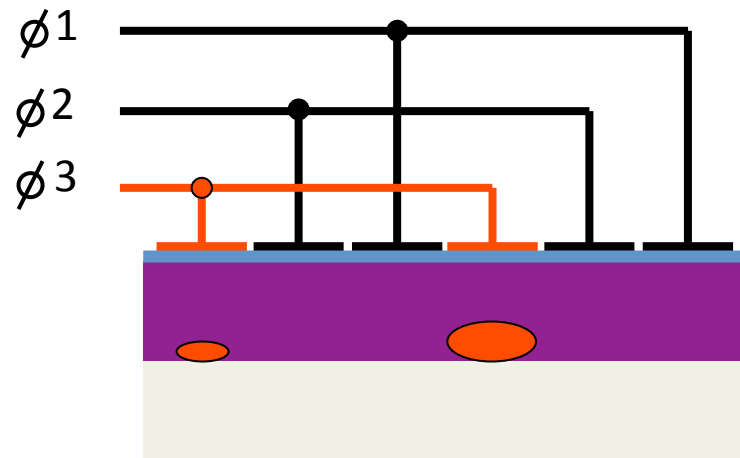
Photons entering the CCD create electron-hole pairs. The electrons are then attracted towards the most positive potential in the device where they create 'charge packets'. Each packet corresponds to one pixel



## Charge Transfer in a CCD 1.

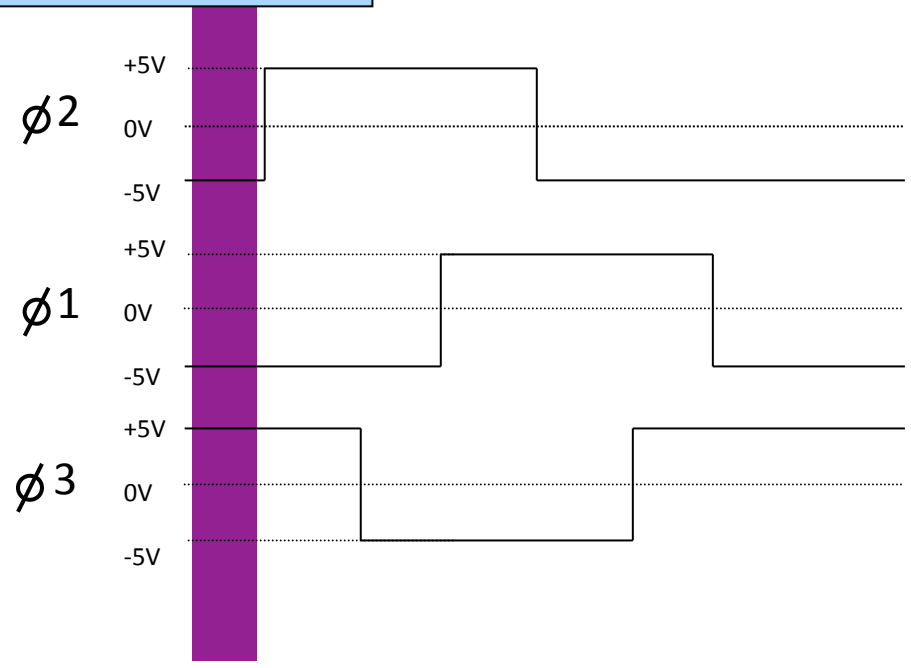
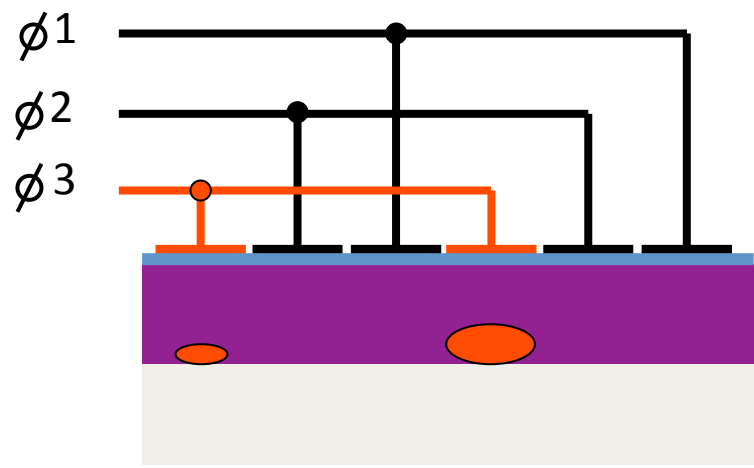
In the following few slides, the implementation of the 'conveyor belts' as actual electronic structures is explained.

The charge is moved along these conveyor belts by modulating the voltages on the electrodes positioned on the surface of the CCD. In the following illustrations, electrodes colour coded red are held at a positive potential, those coloured black are held at a negative potential.



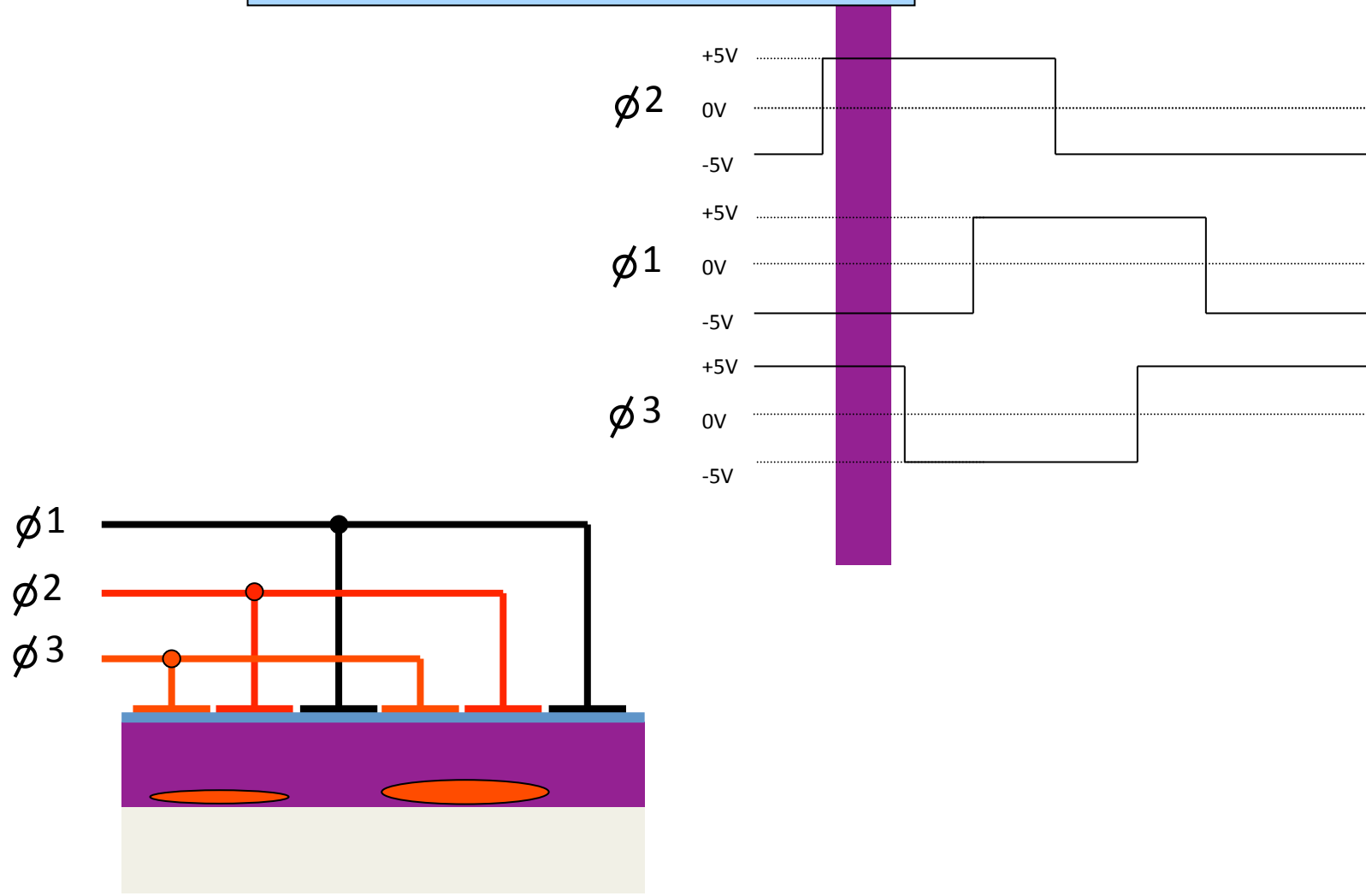


# Charge Transfer in a CCD 2.

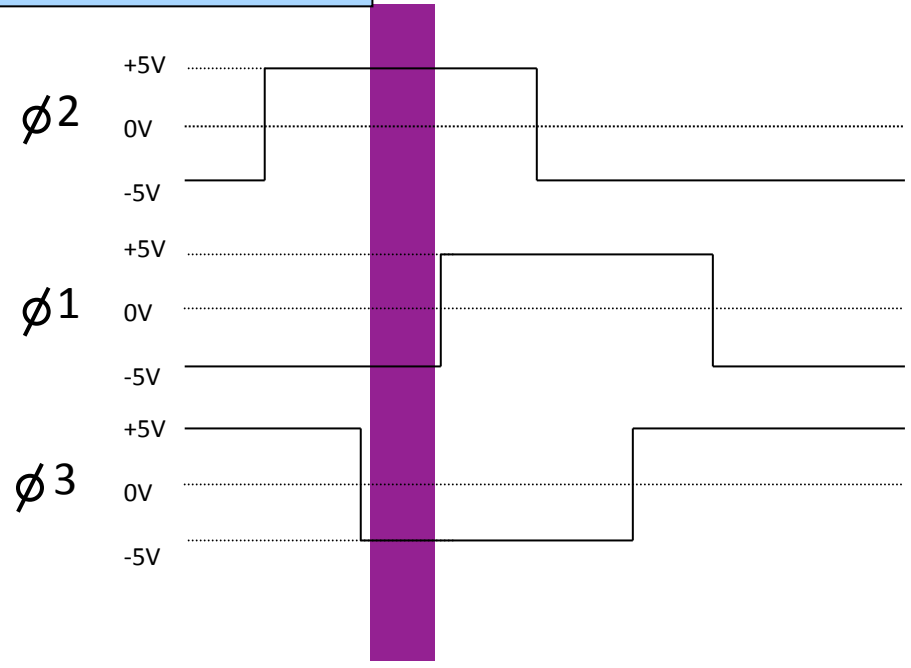
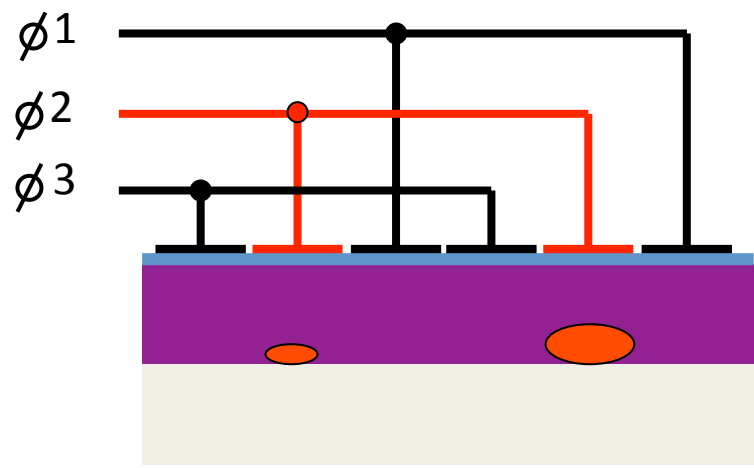


Time-slice shown in diagram

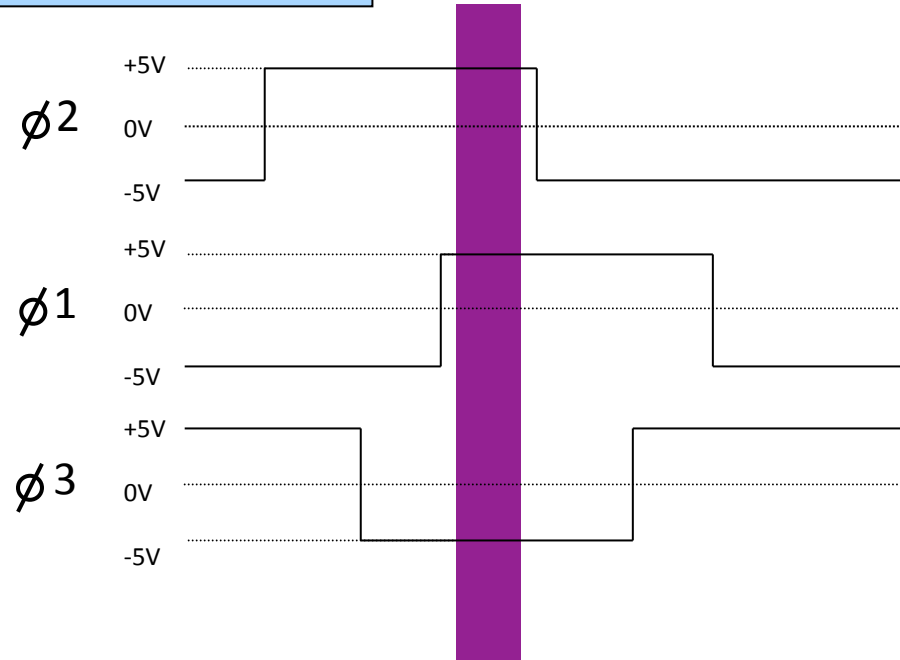
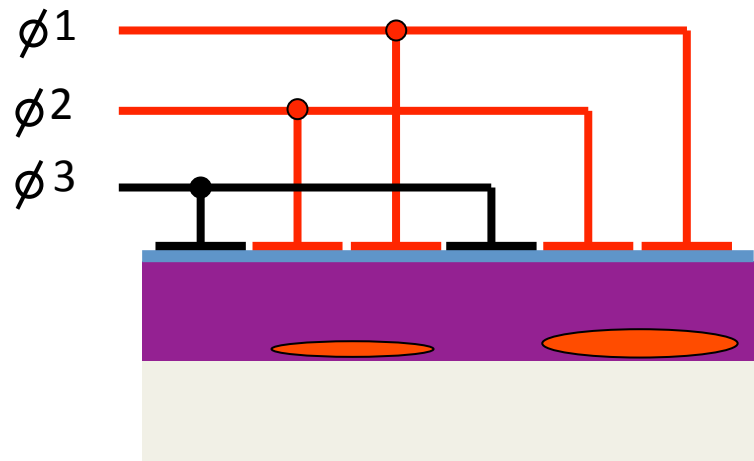
# Charge Transfer in a CCD 3.



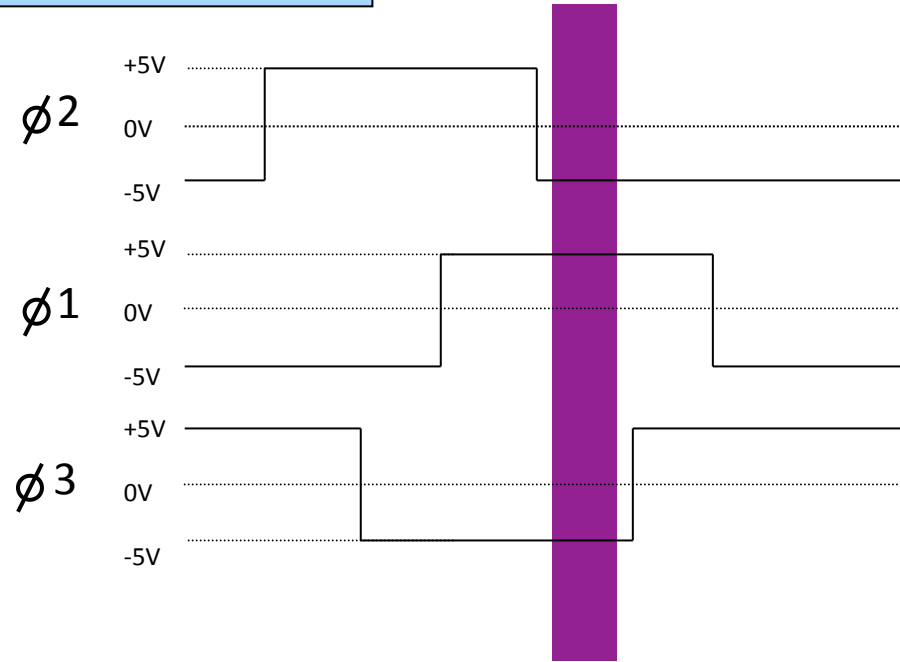
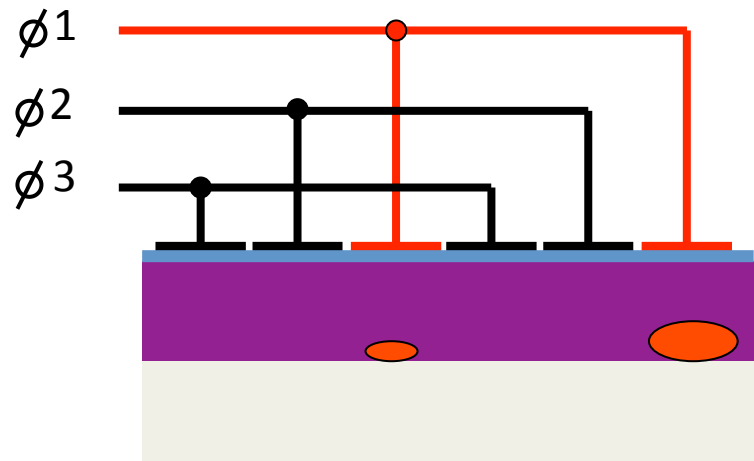
# Charge Transfer in a CCD 4.



# Charge Transfer in a CCD 5.

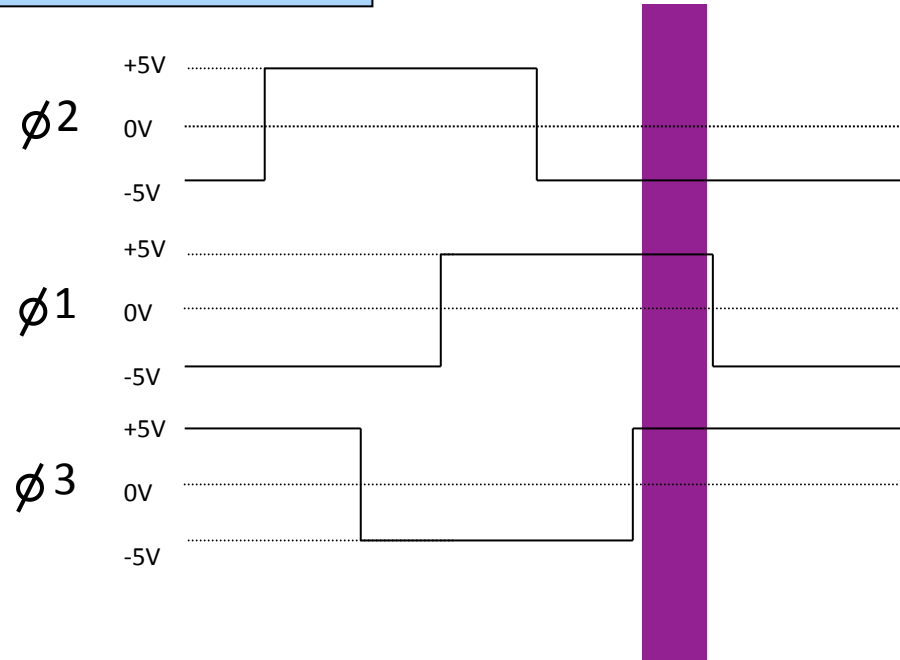
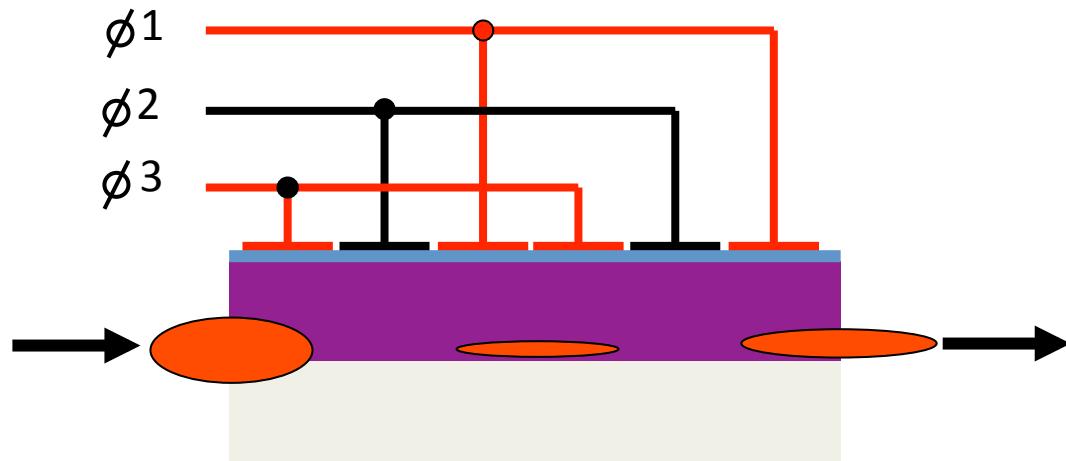


# Charge Transfer in a CCD 6.



# Charge Transfer in a CCD 7.

Charge packet from subsequent pixel enters from left as first pixel exits to the right.



# Charge Transfer in a CCD 8.

